DEPARTMENT OF ELECTRONICS AND COMMUNICATION ENGINEERING

PROGRAM AND SYLLABI

M.Tech in Microelectronics & VLSI



DEPARTMENT OF ELECTRONICS AND COMMUNICATION ENGINEERING NATIONAL INSTITUTE OF TECHNOLOGY

DURGAPUR-713209

CURRICULUM FOR THE M.TECH PROGRAMME

IN

MICROELECTRONICS & VLSI
2017

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1. Curriculum for M. Tech. in Microelectronics & VLSI Department of Electronics and Communication Engineering

FIRST SEMESTER

Sl. No.	Course Code	Name of the Course/ Subject	L	Т	S	C P
1.	EC1011	Semiconductor Device & Modeling	4	0	0	4
2.	EC1012	Analog IC Design	4	0	0	4
3.	EC1013	EC1013 Digital IC Design				4
4.	***	Elective-I	4	0	0	4
5.	***	Elective-II	4	0	0	4
6.	EC1061	Design Lab-I	0	0	4	2
7.	EC1062	Design Lab-II	0	0	4	2
		20	0	8	24	

SECOND SEMESTER

1.	EC2011	VLSI Technology	4	0	0	4
2.	EC2012	VLSI Systems Design	4	0	0	4
3.	***	Elective-III	4	0	0	4
4.	***	Elective-IV	4	0	0	4
5.	***	Elective-V	4	0	0	4
6.	EC2061	Design Lab-III	0	0	4	2
7.	EC2062	Project-I	0	0	4	1
8.	EC2063	Seminar (Non Project)				1
		Total Credit:	20	0	8	24

THIRD SEMESTER

		Total Credit:		26	13
2.	EC3062	Seminar		04	02
1.	EC3061	Project-II		22	11

FOURTH SEMESTER

1.	EC4061	Project-III		22	11	
2.	EC4062	Seminar & Viva-Voce		06	03	
	Total Credit: 28					
		Total Credit:			75	

2. Summary of the Curriculum

Semester	L	Т	S	C	Н
I	20	0	8	24	28
II	20	0	8	24	28
III	0	0	26	13	26
IV	0	0	28	14	28
Grand Total:	40	0	70	75	110
Grand Total (in %): [C / H]	36.36	0	63.64		

3. Distribution of the credit points and contact hours

A. Core Courses:

SI. No.	('nurse Title		Credit	Hours
1.	EC1011	Semiconductor Device & Modeling	4	4
2.	EC1012	Analog IC Design	4	4
3.	EC1013	Digital IC Design	4	4
4.	EC2011	VLSI Technology	4	4
5.	EC2012 VLSI Systems Design		4	4
	•	20	20	
		27.7%	18.2 %	

B. Elective Courses:

SI. No.	Course Code	Course Title	Credit	Hours
1.	EC90xx	Elective – I	4	4
2.	EC90xx	Elective – II	4	4
3.	EC90xx	Elective – III	4	4
4.	EC90xx	Elective – IV	4	4
5.	EC90xx	Elective – V	4	4
		20	20	
		26.7 %	18.2 %	

C. Laboratory:

SI. No.	Course Code	Course Title	Credit	Hours
1.	EC1061	Design Lab I	2	4
2.	EC1062	Design Lab II	2	4
3.	EC2061	Design Lab III	2	4
		Total	6	12
		8 %	10.9 %	

D. Project & Seminar:

SI. No.	Course Code	Course Name	Credit	Hours
1.	EC2062	Project-I	1	2
2.	EC2063	Seminar (Non-Project)	1	2
	EC3061	Project-II Project-II	11	22
3.	EC3062	Seminar	2	4
	EC4061	Project-III Project-III	11	22
4.	EC4062	Seminar & Viva-Voice	3	6
	1	Total	29	58
		Total (%)	38.7 %	52.7 %

4. List of Elective Courses:

S1.	SUBJECT	CLIDIFOT	I T D	CDEDIT
No.	CODE	SUBJECT	L-1-P	CREDIT
1.	EC9011	COOPERATIVE COMMUNICATION NETWORK	4-0-0	4
2.	EC9012	STATISTICAL SIGNAL PROCESSING	4-0-0	4
3.	EC9013	OPTICAL COMMUNICATION	4-0-0	4
4.	EC9014	QUEUING THEORY FOR TELE- COMMUNICATION	4-0-0	4
5.	EC9015	SOFTWARE ENGINEERING	4-0-0	4
6.		COMPUTER SIMULATION OF ELECTRONIC CIRCUITS	4-0-0	4
7.		SPEECH SIGNAL PROCESSING	4-0-0	4
8.	EC9018	IMAGE PROCESSING	4-0-0	4
9.	EC9019	MICROPROCESSORS AND MICROCONTROLLER	4-0-0	4
10.	EC9020	NEURAL NETWORKS	4-0-0	4
11.	EC9021	DETECTION AND ESTIMATION THEORY	4-0-0	4
12.		FIBRE OPTIC NETWORK	4-0-0	4
13.	EC9023	INFORMATION SECURITY AND CRYPTOGRAPHY	4-0-0	4
14.	EC9024	SATELLITE COMMUNICATION	4-0-0	4
15.	EC9025	MICROWAVE CIRCUITS AND TECHNIQUE	4-0-0	4
16.		ADVANCED ANTENNA ARRAY SYNTHESIS	4-0-0	4
17.	EC9027	MICROWAVE MEASUREMENTS AND DESIGN	4-0-0	4
18.	EC9028	NETWORK INFORMATION THEORY	4-0-0	4
19.	EC9029	ANTENNA ANALYSIS AND SYNTHESIS	4-0-0	4
20.	EC9030	ARTIFICIAL INTELLIGENCE AND SOFT COMPUTING	4-0-0	4
21.	EC9031	VOICE AND PICTURE CODING	4-0-0	4
22.	EC9032	OPERATING SYSTEM	4-0-0	4
22	EC9033	MATHEMATICAL METHOD IN	4-0-0	4
23.		TELECOMMUNICATION		
24.	EC9034	DIGITAL SIGNAL PROCESSING & APPLICATION	4-0-0	4
25.	EC9035	TELECOMMUNICATION SYSTEM	4-0-0	4
26.	EC9036	EMBEDDED SYSTEMS	4-0-0	4
27.		BROADBAND COMMUNICATION	4-0-0	4
28.	EC9038	ERROR CONTROL CODING	4-0-0	4
29.		CAD FOR VLSI	4-0-0	4
30.	EC9040	VLSI FOR DIGITAL SIGNAL PROCESSING	4-0-0	4
31.		MIXED SIGNAL IC DESIGN	4-0-0	4
32.		LOW POWER CIRCUITS AND SYSTEMS	4-0-0	4
33.	EC9043	DSP ARCHITECTURES IN VLSI	4-0-0	4
34.		RF IC DESIGN	4-0-0	4
35.		SOC DESIGN	4-0-0	4
36.		FPGA BASED DESIGN	4-0-0	4
37.	EC9047	MEMS & MICROSYSTEMS TECHNOLOGY	4-0-0	4
38.	EC9048	ARCHITECTURAL DESIGN IN IC	4-0-0	4
39.	EC9049	NANOELECTRONICS	4-0-0	4
40.	EC9050	COMPUTER ARCHITECTURE	4-0-0	4
41.	EC9051	TESTING AND VERIFICATION OF VLSI CIRCUITS	4-0-0	4

5. Assessment:

Laboratory Examination (40 + 40 + 20)

For the evaluation of Laboratory Courses, total 100 marks has three components

- a) 40 marks for Continuous Assessment which is based on the performance of the student on day to day basis in Laboratory and results obtained during the experiment done in the Laboratory. Attendance, general attentiveness/ behaviour of student and occasional instant quizzes are also considered in this component.
- b) 40 marks for End-Semester Assessment— which has two subcomponents, 20 marks for performance of the students for experiment or program assigned to the students during the end-semester examination and 20marks for viva-voce examination.
- c) 20 marks for Reports which are written based on the laboratory experiments performed throughout the semester and during the end-semester examination.

Theory Examination

During 2017-2018 and 2018-2019, total 100 marks has three components

- a) 20 marks for Continuous Assessment which is based on quizzes, home assignments and surprise tests.
- b) 30 marks for Mid-Semester Examination which is conducted tentatively within 7-8 weeks after beginning of teaching in each semester.
- c) 50 marks for End-Semester Examination which is conducted at the end of teaching session of the semester.

Based on the feedback taken from the concerned stakeholders of the Institute, PG curriculum has been revised in the academic year 2019-2020. In the new curriculum the evaluation process for the theory subjects is changed as follows.

Continuous assessment 1 (15 marks)

This is realized with class tests, quizzes, home assignments, surprise tests or a combination of these components. If more than two class tests are conducted, the marks are averaged.

Continuous assessment 2 (25 marks, 2 hours)

Mid-term examination covers half of the syllabus. The exam is conducted at the middle of the semester following the academic calendar. The evaluation is done within a fortnight and the answer scripts are shown to the students so that they can understand their shortcomings in learning the subject.

End-term examination (60 marks, 3 hours)

End-term examination covers the full syllabus. The exam is centrally conducted at the end of the semester. After the evaluation, the answer scripts are shown to the students. Model answers are also provided.

6. Program Outcomes (POs) and Program Specific Outcomes (PSOs)

I. Program Outcomes (Pos):

NBA has defined the following three POs for the PG programs:

PO 1: An ability to independently carry out research /investigation and development work to solve practical problems

PO 2: An ability to write and present a substantial technical report/document

PO 3: Students should be able to demonstrate a degree of mastery over the area as per the specialization of the program. The mastery should be at a level higher than the requirements in the appropriate bachelor program

II. Program Specific Outcomes (PSOs):

In addition to the three POs, 3 program specific outcomes (PSOs) have been defined by the Department as follows -

PSO 1 (PO 4): Identify, formulate and solve engineering problems in the field of Microelectronics and VLSI

PSO 2 (PO 5): Apply knowledge, proper methodology and modern tools to analyse and solve the problems in the domain of Microelectronics and VLSI.

PSO 3 (PO 6): Acquire professional and intellectual integrity and ethics of research and recognize the need to engage in learning with a high level of enthusiasm and commitment to contribute to the community for sustainable development of society

Course Articulation Matrices: Connection between the courses and the POs and PSOs

The correlation levels are 1, 2 or 3, denoting: 1: Slight (Low) 2: Moderate (Medium) 3: Substantial (High).

Note: Other than the above-mentioned courses, any course including core and elective offered by another PG program of the Department / Institute can be opted as elective subjects without any constraint.

7. DETAILED SYLLABIOF THE COURSES

A. Core Courses

		Department of El	ectronics and (Communic	cation Eng	gineering		
Course				Total Nu	mber of cor	ntact hours :	40	Credit
Code			Core (PCR) /	Lecture	Tutorial	Practical	Total	
			Electives	(L)	(T)	(P)	Hours	
			(PEL)					
EC1011	Sen	niconductor	PCR	4	0	0	4	4
	Dev	vice & Modeling						
Pre-requisite	es:		Course Assessi	nent metho	ds (Continu	ious (CT) an	d end asse	essment
			(EA))					
		h good background	Assignments,	Quiz, Mid-			and End S	emester
in Semicon	ducto	r Devices			Examinat	ion		
Course		To introduce the p	rinciples of devic	es with em	phasis to M	OS and nanc	-device	
Objectives		operations this is e	•	•				
Course		CO#1: To introduc						e device
Outcomes		modeling of semic			tor materia	is for unders	tanding th	c device
Outcomes			stand the transport of charge carriers for the operation of semiconductor					
		devices.	saint the transport of charge carriers for the operation of semiconductor					nauctor
			iitable approxima	tions and te	echniques to	derive the r	ohysical m	nodel of
			suitable approximations and techniques to derive the physical model of devices such as P-N junctions.					10 001 01
			ze electrostatic variables and current-voltage characteristics of MOS					10S
		devices under a va	<u> </u>					
			te qualitative understanding of the physics of emerging MOS devices					evices
		and conversion of	•	•				
		CO#6: To develop	the fundamental	understand	ing of device	ce modeling	and nume	rical
		simulation						
Syllabus/To	pics	Total Lecture hou	ırs: 40					
Covered								
	Module-I: (L – 08) SEMICONDUCTOR ELECTRONICS: Physics of Semiconductor Materials, Band Model of Solids, Thermal-Equilibrium Statistics, Carriers in Semiconductors, Drift Velocity, Mobility and Scattering, Drift & Diffusion Current, Hall-Effect.							
		Module-II: (L – 0 METAL-SEMICO Semiconductor junction, Step Junc junctions and break	NDUCTOR C nctions, Current- ction, Linearly G	raded junct	haracteristicion, Hetero	cs, Surface junctions, Re		

Module-III: (L - 08)

FIELD-EFFECT TRANSISTORS (MOSFETs): PHYSICAL EFFECTS AND MODELS:MOS Capacitor, Flat Band Voltage, Oxide and Interface Charge, High and Low Frequency C-V Characteristics: Origin and Experimental Determination. Charge- Coupled Devices, non-volatile memory.

Basic MOSFET behavior, MOSFET scaling and short channel behavior. Devices: Complementary MOSFETs (CMOS), electric fields and velocity-saturation, basic leakage currents, channel length modulation, body bias effect, threshold adjustment, sub-threshold conduction.

Module-IV: (L - 08)

Short Channel Effects: Limitation of long channel analysis, short-channel effects: velocity saturation, device degradation, channel length modulation, body bias effect, threshold adjustment, mobility degradation, hot carrier effects, MOSFET scaling goals, gate coupling, velocity overshoot, high field effects in scaled MOSFETs, substrate current and other effects in scaled MOSFETS.

Moore law, Technology nodes and ITRS, Physical & Technological Challenges to scaling, nonconventional MOSFET- (FDSOI, SOI, Multi-gate MOSFET)

Module-V: (L-05)

Modeling: SPICE transistor modeling, compact MOSFET modeling approaches, history of BSIM models, BSIM family of Compact device models, BSIM6 model, BSIM-CMG model, BSIM-IMG model, physics of nanoscale MOSFET, and Design issues of nanoscale MOSFET: challenges of nanoscale MOSFET, scaling trends of MOSFETs, issues for nanoscale MOSFETs (short channel effects), key issues in modeling of MOSFET.

Module-VI: (L - 05)

Numerical Simulation: Numerical simulation, basic concepts of simulations, grids, device simulation and challenges. Importance of semiconductor device simulators - Key elements of physical device simulation, historical development of the physical device modeling.

Introduction to the TCAD Simulation Tool, Examples of TCAD Simulations – MOSFETs and SOI

Text / Ref.

Text Books:

Books

- 1. Advanced Semiconductor Devices by Taur and Ning.
- 2. Device Electronics for Integrated circuits by Muller and Kammins.
- 3. Computational Electronics: Semiclassical and Quantum Device Modeling and Simulation by Dr. Vagica Vasileska and Stephen M. Goodnick.
- 4. Semiconductor Device Modelling by A B. Bhattacharyya.

References:

- 1. Physics of Semiconductor Devices by S. M. Sze and Kwok K. Ng, 3rd Edition, (John Wiley & Sons, 2002).
- 2. Semiconductor Device Fundamentals by Robert F. Pierret, Addison-Wesley Publishing, 1996
- 3. Semiconductor Physics and Devices by Donald A. Neamen, 3rd Edition, Mc Graw Hill, 2003
- 4. Semiconductor Devices- Basic Principles", by Jasprit Singh, John Wiley and Sons Inc., 2001

EC 1011: Semiconductor Device Modeling (Core) [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	To introduce the physics of semiconductor materials for understanding the device modeling of semiconductor devices.	1	1	3	2	1	1
CO 2	To understand the transport of charge carriers for the operation of semiconductor devices.	2	1	3	2	1	1
CO 3	To apply suitable approximations and techniques to derive the physical model of semiconductor devices such as P-N junctions.	2	2	3	2	3	1
CO 4	To analyse electrostatic variables and current-voltage characteristics of MOS devices under a variety of conditions.	2	2	3	3	2	1
CO 5	To evaluate qualitative understanding of the physics of emerging MOS devices and conversion of this understanding into modeling.	2	2	3	3	3	2
CO 6	To develop the fundamental understanding of device modeling and numerical simulation	3	3	3	3	3	2
	Average	2	1.83	3	2.5	2.17	1.33

		nt of Electronics and								
Course	Title of the course	Program Core		Total Number of contact hours: 40						
Code		(PCR) /	Lecture	Tutorial	Practical	Total				
		Electives (PEL)	(L)	(T)	(P)	Hours				
EC1012	Analog IC Design	PCR	4	0	0	4	4			
Pre-requisi	ites / Co-requisites	Course Assessmen (EA))	nt methods (Continuous	s (CT) and er	nd assessn	nent			
Semicondo Circuit De	actor Devices, Analog esign	Assignments, Qui Examination	Assignments, Quiz, Mid-semester Examination and End Semester							
Course Objective		ndation on the design ents to the fundamenta				grated circ	uits and			
Course Outcomes	CO#2: Draw the CO#3: Design b	CO#1: Analyze MOSFET based circuits CO#2: Draw the small signal models of MOS transistors CO#3: Design basic Amplifiers using CMOS CO#4: Illustrate the operation of a Differential amplifier								
through the	_	the frequency respon								
course, CO#6: Identify the various design metrics of analog Design.										
student will be able to CO#7: Compare different types of Layout followed in Analog IC Design										
Topics	Total Lecture l	ours: 40								
Covered/ Syllabus Module-I: (L – 05) MOSFET Operation & Model: Device Structure I/V characteristics, second effects, Capacitances, body bias effect, DIBL, MOS small signal Models, Technology Module-II: (L – 06) Basic Analog blocks: Basic concepts of amplification and biasing, Current source sinks, Current mirrors: Simple current mirror, cascode current mirror, low vacurrent mirror, Wilson and Widlar current mirrors, voltage and current referencement conveyer.						ces and voltage				
	triode load, CS	mplifier : Common so	er: Common source stage with resistive load, diode connected load, with source degeneration, source follower, CG stage, Gain boosting							
	Differential a errors due to amplifier wit	Module-IV: (L – 07) Differential amplifier: Quasi differential amplifier, significance of tail current source, errors due to mismatch, qualitative analysis, common mode response, differential amplifier with MOS loads, single ended conversion. Differential amplifier-characterization, ICMR, Slew Rate, PSRR, offset,								
	Device capac	esponse of Amplifiers: Device high-frequency small-signal models; citances, ft calculation, Simplified high-frequency analysis of basic iller's theorem, OCTC method for BW estimation. cascode amplifiers,								
		z – 04) plifier : Feedback con edback, Practical fe		_		_				

	Procedure for the feedback amplifiers.
	Module-VII: (L – 04) Layout: Introduction to Layout, Fingering, Inter-digitization, Common Centroid, Process gradients, electro-migration and antenna effect
Text Books, and/or	 Text Books: Design of Analog CMOS Integrated Circuits, by Behzad Razavi, McGraw-Hill Analysis and Design of Analog Integrated Circuit, Paul R. Gray, Paul J. Hurst, Stephen H. Lewis, and Robert G. Meyer, John Wiley & Sons Adel S. Sedra, Kenneth C. Smith: Microelectronics Circuits, Oxford University Press
Reference material	 Reference Books/materials: 1. R. L Geiger, Allen and Stradder, VLSI Design Techniques for Analog and Digital Circuits, McGraw-Hill Education, 2010. 2. CMOS: Circuit Design, Layout, and Simulation by R. Jacob Baker, Wiley-IEEE Press(2019)

EC 1012: Analog IC Design (Core)[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	CO Statement			PO 3	PSO 1	PSO 2	PSO 3
CO 1	Analyze MOSFET based circuits.	2	1	2	1	1	1
CO 2	Draw the small signal models of MOS transistors.		2	3	2	2	1
CO 3	Design basic Amplifiers using CMOS.	2	2	3	3	2	1
CO 4	Illustrate the operation of a Differential amplifier.	2	2	3	3	3	1
C0 5	Compute the frequency response of the amplifiers.	2	2	3	3	3	1
CO 6	Identify the various design metrics of analog Design.	2	2	3	3	2	1
Co 7	Compare different types of Layout followed in Analog IC Design.	2	2	3	3	2	1
Average			1.86	2.86	2.57	2.14	1

	Department	of Electronics and (Communic	ation Engi	neering					
Course		Program Core	Total	Number of	contact hour	s: 40				
Course Code	Title of the course	(PCR) / Electives (PEL)	Lecture (L)	Tutorial (T)	Practical (P)	Total Hours	Credit			
EC1013	Digital IC Design	PCR	4	0	0	4	4			
Pr	e-requisites		Course Assessment methods: (Continuous (CT), Mid-semester assessment (MA) and end assessment (EA)):							
Digital Ci	rcuits and Systems	Assignments, Q	Assignments, Quiz, Mid-semester Examination and End Semester Examination							
Course	To study the characte	ristics of CMOS inve	erter, interc	onnects, co	mbinational a	and seque	ntial			
Objectives	circuits and knowledge on Electronic Design Automation (EDA) tools in VLSI and experiment with the current technology/process, and able to design state-of-the-art CMOS circuits.									
Course CO#1: Acquire idea about the digital IC design techniques. Outcomes										
Outcomes	CO#2: Understand th									
	CO#3: Learn the basi	•			•					
	CO#4: Analyze the static and dynamic characteristics of CMOS circuits CO#5: Design and implementation of combinational and sequential circuits									
		•		and sequent	tial circuits					
	CO#6: Evaluate the p		S circuits							
Topics Covered	Total Lecture hours	: 40								
Covered	Module-I:(L -02) Overview of VLSI I VLSI design flow, d design styles, design	lesign hierarchy, con	ncepts of re	egularity, n	nodularity, a	•	_			
	Module-II:(L –03) MOS Transistor TI Long-channel I-V c characteristics.	-								
	Module-III(L – 06) ASIC Design Flow: Introduction to ASIC and SoC, Overview of ASIC flow, functional verification, RTL-GATE level synthesis, synthesis optimization techniques, pre-layout timing verification, static timing analysis, floor-planning, placement and routing, extraction, post layout timing verification, extraction.									
Module-IV:(L –02) CMOS Process Technology: Fabrication process flow- basic steps, the CMOS layout design rules, stick diagram, full-custom mask layout design.						OS n-Wel	l process,			
	Module-V:(L -04) MOS Inverter (St	atic Characteristic	es): Resisti	ve-load in	verter, inve	rter with	n-type			

MOSFET load, CMOS inverter.

Module-VI:(L –06)

MOS Inverters (Switching Characteristics and Interconnects effects): Delay-time definitions, calculation of delay times, logical efforts, inverter design with delay constraints, estimation of interconnect parasitics, calculation of interconnect delay, Bus vs. Network-on-Chip (NoC), switching power dissipation of CMOS inverters.

Module-VII:(L –05)

Combination CMOS Logic Circuits: MOS logic circuits with depletion nMOS loads, CMOS logic circuits, complex logic circuits, CMOS transmission gates (pass gates), ratioed, dynamic and pass transistor logic circuits.

Module-VIII:(L –04)

Sequential MOS logic circuits: Behaviour of bi-stable elements, SR latch circuits, clocked latch and flip-flop circuits, CMOS D-latch and edge-triggered flip-flop. Timing path, Setup time and hold time static, example of setup and hold time static, setup and hold slack, clock skew and jitter, Clock, reset and power distributions.

Module-IX: (L –04)

Semiconductor Memories: Memory Design, SRAM, DRAM structure and implementations.

Module-X:(L –04)

Recent Trends in VLSI Design & its research issues in industry: System case studies. Design automation of VLSI Systems: basic concepts. Deep Sub-micron Technologies: Some Design Issues.

Text Books, and/or reference material

Text Book

- 1. N. H. E. Weste and C. Harris, "Principles of CMOS VLSI Design: A System Perspective, 3rd Edition, Pearson Education 2007.
- CMOS Digital Integrated Circuits, Sung-Mo Kang, YusufLeblebici, 3rd edition, Tata McGraw-Hill, 2003

References:

1. J. Rabaey, A. Chandrakasan and B. Nikolic, Digital Integrated Circuits: A Design Perspective, 2nd Edition, Prentice Hall 2004.

EC 1013: Digital IC Design (Core)[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Acquire idea about the digital IC design techniques.	1	1	2	2	3	2
CO 2	Understand the characteristics of CMOS inverter	1	1	2	2	3	1
CO 3	Learn the basic steps of ASIC Design Flow and fabrication process.	1	1	2	3	3	3
CO 4	Analyze the static and dynamic characteristics of CMOS circuits	2	1	2	3	3	1
C0 5	Design and implementation of combinational and sequential circuits	1	1	2	3	3	2
CO 6	Evaluate the performance of CMOS circuits	1	1	2	3	3	1
Average			1	2	2.67	3	1.67

Code		Department	of Electronics and (Communic	ation Engi	neering					
Course Code Title of the course (PCR) / Electives (PEL) EC2011 VLSI Technology PCR 4 0 0 0 4 4 Pre-requisites Course Assessment methods: (Continuous (CT), Mid-semester assessment (MA) and end assessment (EA)): Semiconductor Device and Modeling (EC1011) Assignments, Quiz, Mid-semester Examination and End Semester Examination Course Objectives Course Outcomes CO#1: Outline the basics of semiconductor crystal properties CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication, CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L - 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L - 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L - 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L - 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L - 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.			Program Core	Total	Number of	contact hour	s: 40				
Pre-requisites Course Assessment methods: (Continuous (CT), Mid-semester assessment (MA) and end assessment (EA)): Semiconductor Device and Modeling (EC1011) Assignments, Quiz, Mid-semester Examination and End Semester Examination Course Objectives Course Objectives Course Outcomes CO#1: Outline the basics of semiconductor crystal properties CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.		Title of the course	(PCR) / Electives	Lecture	Tutorial	Practical	Total	Credit			
Semiconductor Device and Modeling (EC1011) Assignments, Quiz, Mid-semester Examination and End Semester Examination Course Objectives Course Outcomes CO#1: Outline the basics of semiconductor crystal properties CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.	EC2011	VLSI Technology	PCR	4	0	0	4	4			
Course Objectives Course Outcomes CO#1: Outline the basics of semiconductor crystal properties Cottcomes CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.	Pr	e-requisites						ster			
Course Outcomes CO#1: Outline the basics of semiconductor crystal properties Outcomes CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-IV: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.											
Outcomes CO#2: Identify the fundamentals of IC fabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.		To study the various processes of IC fabrication									
CO#2: Identify the fundamentals of IC Tabrication CO#3: Illustrate the different methods involved in VLSI fabrication process CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Total Lecture hours: 40 Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.		CO#1: Outline the basics of semiconductor crystal properties									
CO#4: Appreciate the advanced methods involved in IC fabrication. CO#5: Build the knowledge of process integration-NMOS, CMOS. Syllabus/ Topics Covered Total Lecture hours: 40 Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.	Outcomes	Outcomes CO#2: Identify the fundamentals of IC fabrication									
Syllabus/ Topics Covered Total Lecture hours: 40 Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.		CO#3: Illustrate the different methods involved in VLSI fabrication process									
Syllabus/ Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.		CO#4: Appreciate the advanced methods involved in IC fabrication.									
Topics Covered Module-I: (L – 01) Introduction: History of IC's; Operation & Models for Devices of Interest: CMOS and MEMS. Module-II: (L – 02) Electronic Materials: Crystal Structures, Defects in Crystals, Si, Poly Si, Si Crystal Growth. Module-III: (L – 03) Clean room and Wafer Cleaning: Definition, Need of Clean Room, RCA cleaning of Si. Module-IV: (L – 05) Oxidation: Dry and Wet Oxidation, Kinetics of Oxidation, Oxidation Rate Constants, Dopant Redistribution, Oxide Charges, Device Isolation, LOCOS, Oxidation System Module-V: (L – 05) Lithography: Overview of Lithography, Radiation Sources, Masks, Photoresist, Components of Photoresist Optical Aligners, Resolution, Depth of Focus, Advanced Lithography: E-beam Lithography, X-ray Lithography, Ion Beam Lithography.											
Diffusion: Pre-Deposition and Drive-in Diffusion Modeling, Dose, 2-Step Diffusions, Successive Diffusion, Lateral Diffusion, Series Resistance, Junction Depth, Irvin's Curves, Diffusion System. Module-VII: (L – 05) Ion Implantation: Problems in Thermal Diffusion, Advantages of Ion Implantation, Applications in ICs, Ion Implantation System, Mask, Energy Loss Mechanisms, Depth Profile,	Covered	Introduction: Histo MEMS. Module-II: (L – 02) Electronic Materials Module-III: (L – 03) Clean room and Wa Module-IV: (L – 05) Oxidation: Dry and Redistribution, Oxide Module-V: (L – 05) Lithography: Overv of Photoresist Optical Lithography, X-ray L Module-VI: (L – 05) Diffusion: Pre-Deposite Successive Diffusion Diffusion System. Module-VII: (L – 05) In Implantation:	s: Crystal Structures, afer Cleaning: Defin Wet Oxidation, Kine Charges, Device Iso iew of Lithography, Il Aligners, Resolution atthography, Ion Bear osition and Drive-in, Lateral Diffusion, Problems in The	Defects in Defects in Need etics of Oxiolation, LO Radiation on, Depth on Lithograp n Diffusion Series Re	Crystals, Some of Clean Resident dation, Oxide COS, Oxide Sources, Months of Focus, Albay.	i, Poly Si, Si oom, RCA c dation Rate C ation System asks, Photore dvanced Lith ag, Dose, 2 nction Deptl	Crystal G leaning of Constants, esist, Com nography: -Step Dif h, Irvin's	rowth. Si. Dopant aponents E-beam Clusions, Curves,			

Implantation Annealing, Ion Channeling, Multi Energy Implantation. **Module-VIII:** (L-05)Thin Film Deposition: Physical Vapor Deposition: Thermal evaporation, Resistive Evaporation, Electron beam evaporation, Laser ablation, Sputtering Chemical Vapor Deposition: Advantages and disadvantages of Chemical Vapor deposition (CVD) techniques over PVD techniques, reaction types, Boundaries and Flow, Different kinds of CVD techniques: APCVD, LPCVD, Metallorganic CVD (MOCVD), Plasma Enhanced CVD etc. **Module-IX:** (L-02)Etching: Anisotropy, Selectivity, Wet Etching, Plasma Etching, Reactive Ion Etching. **Module-X:** (L-04)Metallization/Interconnects: Overview of Interconnects, Contacts, Metal gate/Poly Gate, Metallization, Problems in Aluminum Metal contacts, Al spike, Electromigration, Metal Silicides, Multi-Level Metallization, Planarization, Inter Metal Dielectric. **Module-XI:** (L-03)NMOS, CMOS process etc. Text Books. **Text Books:** and/or 1. VLSI Technology, S. M. Sze, 2nd Edition, McGraw Hill, 2003. reference 2. Silicon Process Technology, S K Gandhi, 2nd Edition, Wiley India, 2009 material

References:

- 1. Silicon VLSI Technology, Plummer, Deal and Griffin ,1st Edition, Pearson Education,2009
- 2. Fundamental of Semiconductor Fabrication, Sze and May,2nd Edition, Wiley India,200

EC 2011: VLSI Technology (Core)
[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Outline the basics of semiconductor crystal properties	1	1	3	2	1	1
CO 2	Identify the fundamentals of IC fabrication	1	1	3	3	2	1
CO 3	Illustrate the different methods involved in VLSI fabrication process	2	2	3	2	3	1
CO 4	Appreciate the advanced methods involved in IC fabrication	2	2	3	3	3	1
CO 5	Build the knowledge of process integration-NMOS, CMOS	3	3	3	3	3	1
	1.8	1.8	3	2.6	2.4	1	

	Department of	f Electronics and	Communi	cation Eng	gineering					
Course	Title of the course	Program Core	Total Nu	mber of cor	ntact hours : 4	40	Credit			
Code		(PCR)/	Lecture	Tutorial	Practical	Total				
		Electives (PEL)	(L)	(T)	(P)	Hours				
EC2012	VLSI Systems	PEL	4	0	0	4	4			
	Design									
Pre-requisite	s:	Course Assessme	nt methods:	(Continuo	us (CT), Mid	l-semester				
		assessment (MA) and end assessment (EA)):								
Digital and A	nalog IC/VLSI	Assignments, (Quiz, Mid-so	emester Exa	amination ar	nd End Sei	mester			
Design				Examination	on					
Course		basic concepts of m			•					
Objectives Describe the fundamental principles underlying digital design using CMOS logic analyse the performance characteristics of these digital circuits.							ogic and			
	•	hesizable digital sub		_		HDL				
		sign meets its functi		ng constrai	nts, both mai	nually and	through			
Course		outer-aided design to and the custom and s		digital IC	design flow	in VI SI				
		and the concept of		_	_		ling and			
Outcomes		on and learn how to apply these to multimillion gate designs.								
	Co#3: Learn to	design a digital sys	design a digital system without any timing issues by understanding the							
		iated with such syste					oises.			
	-	and interpret the des	-	_	-	-				
	-	and analyse the perf	formance (s	peed, powe	er) of CMOS	digital in	itegrated			
Syllabus/Top		erent specifications.								
Covered	Total Lecture	110u15. 40								
Covered		07) ology: Structured de design; cell based								
		- 05) systems: Adders; O wer and Speed Trade		tectors; Co	mparators; (Counters;	Shifters;			
		1–05) Array Subsystems: Memory controller and management, SRAM, DRAM, excess memories; CAM, PLAs; Array yield, reliability; Power dissipation in								
	Module-IV:(L Special purpose	- 05) Subsystems: Packaging; power distribution; I/O pads;								
		- 05) nterconnect parame tics; Inductive paras								
Module-VI:(L-05)										

	Timing Issues: Timing classification; Synchronous design; Self-timed circuit design; Module-VII:(L – 08) Clock Synthesis and Synchronization: Synchronizers; Arbiters; Clock Synthesis; PLLs; Clock generation; Clock distribution; Synchronous Vs Asynchronous Design. GPIO, UART, USART, I2C and CAN.
Text / Ref.	Text Books:
Books	 Neil H. E. Weste, David. Harris and Ayan Banerjee, "CMOS VLSI Design" - Pearson Education, Third Edition, 2004. Jan M. Rabaey, Anantha Chandrakasan, Borivoje Nikolic, "Digital Integrated Circuits" Pearson Education, Second Edition.
	References: 1. Sung-Mo Kang, Yusuf Leblebici, "CMOS Digital Integrated Circuits" TMH, Third Edition, 2003 2. Wayne Wolf, "Modern VLSI Design", 2nd Edition, Prentice Hall, 1998.

EC 2012: VLSI Systems Design (Core)
[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 2	PSO 2	PSO 3
CO 1	Understand the custom and semi-custom digital IC design flow in VLSI.	1	1	2	1	1	1
CO 2	Understand the concept of logic synthesis, optimization, and scheduling and resource allocation and learn how to apply these to multimillion gate designs.	2	1	2	3	2	1
CO 3	Learn to design a digital system without any timing issues by understanding the Problems associated with such systems like slack, skew, jitter and interconnect noises.	2	2	3	3	3	1
CO 4	Identify and interpret the design towards realizing digital IC design.	2	2	2	3	3	1
CO 5	Design and analyse the performance (speed, power) of CMOS digital integrated circuits for different specifications.	3	2	3	3	3	1
	Average			2.4	2.6	2.4	1

B. Laboratory Courses

	Department	of Electronics and	Communic	ation Engi	neering					
Course	Title of the course	Program Core	Total Nu	mber of cor	tact hours		Credit			
Code		(PCR) /	Lecture	Tutorial	Practical	Total				
		Electives (PEL)	(L)	(T)	(P)	Hours	_			
EC1061	Design	Lab	0	0	4	4	2			
	Laboratory I									
	(Analog IC Design)									
Pre-requisi	ites / Co-requisites	Course Assessmen	t methods (Continuous	(CT) and er	d accecem	nent			
	wledge of Linux and	(EA))	it inctitous (Continuous	s (C1) and ci	ia assessii	iciit			
Devices / ((212))								
NIL		CT+EA								
Course	To Design and	characterize CMOS	Analog blo	cks using	CAD tools i	n Moderr	CMOS			
Objective	process.									
Course		ugh the course, stude	nt will be ab	ole to						
Outcomes	CO#1: Operate (CAD tools (Cadence/	Mentor) to	simulate Ar	nalog blocks	in Modern	n CMOS			
	process.									
		ne the characteristic	es of active	e/ & passi	ve devices f	for model	ling and			
	analysis.									
	CO#3: Design an inverter (and other basic gates) based on the given specifications. CO#4: Optimize a Differential amplifier to meet the target specification									
	_	te various performa				PSRR SR	Power			
	~ ~	ay, and Noise Margin				bidit, bit	i, Tower			
	_	the effect of process	•	_		tion				
		1		C						
Topics	List of experime	ents								
Covered/										
Syllabus		nation of NMOS and			(T. 1 1 0	aa\				
		nation of NMOS and		•		γ , SS)				
		on of NMOS and PM on of CMOS Inverter				in nower				
		of a voltage reference			_	iii, powei				
		& simulation of Com			ment minor					
	_	on of Ring Oscillator		F						
		arlo Simulation and		ation						
Text/	https://pope	2. Cadence Tutorials: https://papa.wiki.if.via.ne/Cadence Tutorial English and ange 6.1.6								
Reference	Codence Tr	https://nano.wiki.ifi.uio.no/Cadence-Tutorial-English-cadence_6.1.6 Cadence Tutorials:								
materia			el/UCEXco	ıvlc45iam5	ca6vvEG7A					
		https://www.youtube.com/channel/UCEXcqylc45jam5xa6vvEG7A https://www.youtube.com/channel/UCM84pD-OsnS4-O3tTsr8gZA								

EC 1061: Design Laboratory I [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Operate CAD tools (Cadence/Mentor) to simulate Analog blocks in Modern CMOS process.	3	1	2	2	2	1
CO 2	Determine the characteristics of active/ & passive devices for modeling and analysis.	1	1	3	3	3	1
CO 3	Design an inverter (and other basic gates) based on the given specifications.	2	2	3	3	3	1
CO 4	Optimize a Differential amplifier to meet the target specification	3	1	2	2	2	1
CO 5	Appreciate various performance metrics like CMRR, ICMR, PSRR, SR, Power Dissipation, Delay, and Noise Margin with respect to design variables.	1	1	3	3	3	1
CO 6	Examine the effect of process variation using Monte Carlo simulation	3	1	2	2	2	2
	Average	2	1.2	2.6	2.6	2.6	1

		Departm	ent of Electronics and	Communica	tion Engine	ering			
Course	Tit	le of the course	Program Core	Total Nu	mber of con	tact hours		Credit	
Code			(PCR) /	Lecture	Tutorial	Practical	Total		
			Electives (PEL)	(L)	(T)	(P) [#]	Hours		
EC1062		sign Laboratory I gital IC Design)	I PCR	0	0	4	4	2	
Pre-requisi	ites/C	Co-requisites	Course Assessmen	nt methods	(Continuous	s evaluation	(CE) and e	end	
-		_	assessment (EA))						
•		Basic Electronic	s, CE+EA						
		Devices, and							
Digital Ele									
	Des	ign (EC1012)	.1	*** G* 1 .					
Course			the concepts of digital			7D A 40 olo			
Outcomes			anding of HDL coding the combinational and			EDA toois			
			ind implementation of			nential circu	ite		
			e the performance of di			uchtiai cheu	11.5		
Topics		List of experi		8	<u>~</u>				
Covered		•							
			and Implementation o		onal circuit	s using data	flow or ga	te level	
			ling along with their tes	st bench					
		I.	Basic Gates						
		II.	Half-Adder and Full-						
		III.	Half-Subtractor and I	Full-Subtrac	ctor				
		IV.	2:4 Decoder						
		V.	8:3 Encoder						
		VI.	•	Parity Checker					
		VII.	8:1 Multiplexer						
		VIII.	1:4 De-multiplexer						
		IX.	Binary to gray conver						
		X.	Gray to binary conve						
		XI.	2-bit magnitude comp	oarator					
		2. Design	and Implementation o	f sequential	l circuits ald	ong with thei	r test benc	h	
		I.	Design and simulation	•	ops (RS FF,	JK FF, T FF	F, D FF& I	Master-	
		II.	slave FF) using VHD Design and simulatio		ra (Synahra	mous and As	vnahrana	uc) ucina	
		11.	VHDL\ Verilog.	ii oi Counte	as (Syncino	nious and As	Syncinono	us) using	
		III.	Design and Simulation using VHDL\ Verilog		egisters (SIS	SO, SIPO, P	ISO & PIF	PO)	
		IV.	Design an Arithmetic		VHDL\ Vei	rilog.			
		3. Spec.	to GDSII using Synops	ys tools					
		interna correc	fications: Two count ally generated clock. Al ally. Total 40 flip-flips only four outputs and tw	l clocks had nowhere no	ve to be idented the limit	ntified for sta t in terms of	atic timing f area for	to work this chip	

Text Books,	Suggested Text Books:
and/or	1. Samir Palnitkar, Verilog HDL, Second Edition, Pearson education 2003
reference	2. Design of Analog CMOS Integrated Circuits, by Behzad Razavi, McGraw-Hill
material	3. Cadence Design Tutorials in YouTube.

EC 1062: Design Laboratory II [Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Acquire the concepts of digital VLSI design	3	1	2	2	2	1
CO 2	Understanding of HDL coding and simulation using EDA tools	1	1	3	3	3	1
CO 3	Analyze the combinational and sequential circuits	2	2	3	3	3	1
CO 4	Design and implementation of combinational and sequential circuits	2	2	3	3	3	1
CO 5	Evaluate the performance of digital circuits	2	2	3	3	3	1
	Average	2	1.6	2.8	2.8	2.8	1

	Department	of Electronics and	Communic	ation Engi	neering		
Course	Title of the course	Program Core	Total Nu	mber of cor	ntact hours		Credit
Code		(PCR) /	Lecture	Tutorial	Practical	Total	
		Electives (PEL)	(L)	(T)	(P)	Hours	
EC2061	Design Lab III	Lab	0	0	4	4	2
	(Mixed Signal IC Design)						
Pre-requisi	tes / Co-requisites	Course Assessmen (EA))	nt methods ((Continuous	s (CT) and er	nd assessn	nent
NIL		CT+EA					
Course		es CMOS schemati					
Objective		place & route and ti		cation. Enti	re EDA Too	l flow for	a Mixed
		be introduced in this					
Course	1 2	AD tools to carry out			_	up appro	ach
Outcomes		m/ID plots and its us			esign		
		amps to meet any gi	ven specific	ation			
	CO#4 Design of a		Des larrout	Pr Doot I over	out manfanna		
	CO#3 Draw the I	Layout and compare	Pre-layout a	x Post Layo	out performa	nce	
Topics	List of experime	nts:					
Covered/							
Syllabus		on of gm/ID plots for			hs.		
		nd simulation of Cor					
	_	nd optimze a Single	•	•			
	_	nd optimize a Two s		p			
		f Band-gap reference		/ T . 1			
		nd Simulation of a C			TT .		
7. Design of 8 bit Flash ADC and measure its DNL, INL etc.					4:		
8. Layout of CMOS a) Inverter and ii) Opamp & Perform post Layout Simulation using Assura/Calibre							
Referenc		Design of Analog (CMOS Integ	grated Circ	uits, McGra	w-Hill E	ducation,
materials 2002. 2. Allan Hastings, The Art of Analog Layout, Prentice Hall, Second Edition, 2005.						<i>.</i>	

EC 2061: Design Laboratory III[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Employ CAD tools to carry out Mixed Signal	1	1	2	3	3	1
	Design using bottom up approach	_	_	_)	•	_
CO 2	Illustrate gm/ID plots and its use in Analog Circuit Design	2	2	2	3	3	1
CO 3	Design Opamps to meet any given specification	2	2	2	3	3	1
CO 4	Design of a Comparator	3	2	3	3	3	1
CO 5	Draw the Layout and compare Pre-layout & Post Layout performance	3	3	3	3	3	2
	Average	2.2	2	2.4	3	3	1.2

C. Elective Courses

	De	epartment of El	ectronics and C	Communic	cation Eng	gineering						
Course Code	Tit	le of the course	Program Core	Total Nu	mber of cor	ntact hours :	40	Credit				
			(PCR)/	Lecture	Tutorial	Practical	Total					
			Electives	(L)	(T)	(P)	Hours					
			(PEL)									
EC9039	CA	AD for VLSI	PCR	4	0	0	4	4				
Pre-requisites:			Course Assessn	nent metho	<u>l</u> ds (Continu	lous (CT) and	d end asse	ssment				
_												
Digital Design and Programming			Assignments,	Quiz, Mid-s	semester Ex	camination a	and End S	emester				
Language					Examinati	ion						
Course Objectiv	ves	To provide an	introduction to th	e fundame	ntals of Co	mputer-Aide	d Design	tools for				
		the modeling,	design, analysis,	test, and	verification	of digital	Very Lar	ge Scale				
		Integration (VI	LSI) systems.									
Course Outcom	nes	CO#1: Extend	knowledge of C.	AD tools, V	Verilog and	their applic	ations in	Xilinx to				
		verify the circu	iit functionality in	digital dor	nain.							
		CO#2: Introdu	ice students to the	concepts a	nd use of V	erilog in the	Xilinx to	a digital				
		system.										
		CO#3: Provide	e sufficient know	ledge and e	experience s	so that stude	nts will b	e able to				
		make meaning	ful design choice	s when ask	ed to design	n any digital	circuit to	meet or				
		exceed design	specifications.									
Syllabus/Topics	s	Total Lecture l	nours: 40									
Covered		Module-I: (L – Overview of D	03) igital Design wit	h Verilog	HDL: Evol	lution of CA	AD, emer	gence of				
		HDLs, typical H	IDL-based design	flow, Veri	log HDL, T	rends in HD	Ls.					
	Module-II:(L – 03) Hierarchical Modeling Concepts: Top-down and bottom-up design methodolog differences between modules and module instances, parts of a simulation, design block, stimulus block.											
	Module-III: (L – 03) Basic Concepts: Lexical conventions, data types, system tasks, compiler directives. Memory modelling Logic Synthesis: Introduction synthesis of different Verilog constructs.						•					
Module-IV:(L -03) Modules and Ports: Module definition, port declaration, connecting po hierarchical name referencing. Introduction to Reconfigurable computing, FPGAs, Altera /Xilinx flow.												
		Module-V:(L -	02)					Module-V: (L – 02)				

Gate-Level Modeling: Modeling using basic Verilog gate primitives, description of and/or and buf/not type gates, rise, fall and turn-off delays, min, max, and typical delays. **Module-VI:**(L - 03)Dataflow Modeling: Continuous assignments, delay specification, expressions, operators, operands, operator types. Module-VII:(L - 03)**Behavioural Modeling:** Structured procedures, initial and always, blocking and nonblocking statements, delay control, generate statement, event control, conditional statements, multiway branching, loops, sequential and parallel blocks. **Module-VIII:**(L - 04)Tasks and Functions: Differences between tasks and functions, declaration, invocation, automatic tasks and functions. **Module-IX:**(L-04)Useful Modeling Techniques: Procedural continuous assignments, overriding parameters, conditional compilation and execution, useful system tasks. Module-X:(L-04)Flip-Flop and Counter Design: Synchronous and asynchronous flip flop design with set and reset, design of basic counters. **Module-XI:**(L-04)Introduction to FPGAs **Module-X:** (L-04)Essential System Verilog for UVM: Overview of basic SystemVerilog, UVM verification environment: introduction to UVM methodology and universal Verification Components (UVC) structure, stimulus modeling, creating a simple environment, DUT, TLM, functional coverage modeling, register modeling in UVM. Text Books: Text / Ref. Books Verilog HDL, Samir Palnitkar, Second Edition, Pearson Education, 2004 Verilog HDL Synthesis, J. Bhaskar, BS publications, 2001. 1. Fundamentals of

EC 9039: CAD for VLSI (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

Digital Logic

McGraw-Hill Companies, Incorporated, 2007.

with

Verilog Design, Brown &

Vranesic.

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Extend knowledge of CAD tools, Verilog and their applications in Xilinx to verify the circuit functionality in digital domain.	1	1	3	2	2	1
CO 2	Introduce students to the concepts and use of Verilog in the Xilinx to a digital system.	2	1	3	2	2	1
CO 3	Provide sufficient knowledge and experience so that students will be able to make meaningful design choices when asked to design any digital circuit to meet or exceed design specifications.	3	2	3	3	3	1
	Average			3	2.33	2.33	1

~		of Electronics and					Credit
Course	Title of the course	Program Core					
Code		(PCR) /	Lecture Tutorial		Practical Total		
EC 0024	D: '/ 1G' 1	Electives (PEL)	(L)	(T)	(P)	Hours	4
EC 9034	Digital Signal Processing and Applications	PEL	4	0	0	4	4
Pre-requisi		Course Assessme	nt methods	(Continuous	s (CT) and e	nd assessn	nent
~		(EA))					
Mathemati MAC331)	d Systems (ECC303), ics-II & III (MAC	Class Assignment					
Course Objective	and Testing; FIR Transform; Discr Processing of Co Synthesis and De		e and Non in Frequenc mals; Analo	Recursive; y Domain; og Filter D	Discrete For Simple Digital Esign; Digital	urier Trans ital Filters al Filter S	sform; Z ; Digital structure,
Course		given signal or syst			Fourier tran	sform and	Z-
Outcomes	CO#2: Process si a given problem,	withe property of a signals to make them construct simple IIR	more useful and FIR fil	; and how t lter.	-		
CO#3: Design and Analysis of various types of Analog Butterworth and Chebyshev filter CO#4: Design methods to convert analog filters into digital filters. CO#5. Perform Frequency transformations in Analog and Digital domains. Realization of Digital FIR and IIR Filter Structure.							
Topics Covered/	Total Lecture ho	ours: 40					
Syllabus	Module-I: $(L - 0)$ Introduction: rea organization of the	sons behind digital	processing	of signals.	, brief histor	rical deve	lopment,
	stability, differen	te time linear syster ce equations, freque	ncy respons	se, discrete			
Module-III:(L – 05) Z –transform: definition, properties of Z transform, system function, digital fi implementation from the system function, region of convergence in the Z pl determining filter coefficients from the singularity locations, geometric evolution of transform in the Z plane, relationship between Fourier transform and Z transform, invertically transform.						Z plane, on of Z	
Module-IV:(L – 05) Transform technique: Fourier transform, its properties, inverse Fourier transform, discrete Fourier transform, properties of DFT, circular convolution, computations for evaluating the DFT, decimation in time and decimation in frequency FFT algorithms, discrete Hilber transform.						ating the	
Module-V:(L – 04) Digital filter structures: system describing equations, filter categories, All Pass Comb Filters, direct form I and II structures, cascade and parallel communication of order systems, Polyphase representation of filters, linear phase FIR filter structures to the FIR filter.							of second ructures,

Stability using All Pass Functions. **Module-VI:**(L-05)IIR filter design techniques: Analog Filter Design, Analog Butterworth lowpass filter design techniques, Analog Chebyshev LPF, Design methods to convert analog filters into digital filters, frequency transformation for converting lowpass filters into other types, allpass filters for phase response compensation. **Module-VII:**(L - 05)Digital Filter Structures: IIR Realizations, All Pass Realizations, FIR and IIR Lattice Synthesis, IIR Design by Bilinear Transformation, Digital to Digital Frequency Transformation. **Module-VIII:**(L - 05)FIR filter design techniques: Windowing method for designing FIR filters, DFT method for approximating the desired unit sample response, combining DFT and window method for designing FIR filter, frequency sampling method for designing FIR filter. **Module-IX:**(L-04)Non-Linear System Identification Schemes, Fractional-order digital differentiators (DDs) and digital integrators (DIs), Fractional-order low-pass Butterworth and Chebyshev filter. Text Books: 1) Discrete-Time Signal Processing (Second Edition), Alan V. Oppenheim, Ronald W. Schafer, and John R. Buck, Pearson Education India 2) Digital Signal Processing: Principles, Algorithms and Applications (3rd Edition), John G. Proakis, Dimitris G. Manolakis, and D Sharma, Pearson Education India Text Books. 3) Richard G. Lyons, Understanding Digital Signal Processing, Prentice Hall, 1996. and/or 4) Digital Signal Processing by Tarun Kumar Rawat, Oxford University Press. Reference

Reference Books/materials:

material

- 1) S. W. Smith, The Scientist and Engineer's and Guide to Digital Signal Processing, California Technical Publishing, 1997. ISBN: 0-9660176-3.
- 2) Digital Signal Processing using MATLAB, Vinay K. Ingle, John G. Proakis, Brooks/Cole-Thomson Learning

EC 9034: Digital Signal Processing & Applications (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Analyse a given signal or system using tools such as Fourier transform and z-transform to know the property of a signal or system.	3	2	1	3	2	1
CO 2	Process signals to make them more useful; and how to design a signal processor for a given problem, construct simple IIR and FIR filter.	1	2	1	1	1	1
CO 3	Design and Analysis of various types of Analog Butterworth and Chebyshev filters.	3	3	3	3	2	2
CO 4	Design methods to convert analog filters into digital filters.	3	3	3	2	2	2
CO 5	Perform Frequency transformations in Analog and Digital domains. Realization of Digital FIR and IIR Filter Structure.	3	3	2	3	3	3
	Average	2.6	2.6	2	2.4	2	1.8

Course	T:410 0£	Department the course	t of Electronics and C			eering ntact hours: 4	10	Credit
Course Code	1 itie of	tne course	Program Core (PCR) /			1	1	Crean
Code			Electives (PEL)	Lecture (L)	Tutorial (T)	Practical (P)	Total Hours	
EC9041	Mixed S Design	Signal IC	PEL (Elective)	4	0	0	4	4
Pre-requis)	equisites	Course Assessmer (EA))	nt methods	(Continuous	s (CT) and e	nd assessn	nent
	NIL		Class Assignments	s, Quiz, Mi	d and End T	Term examin	ations	
Course Objective	To i	ntroduce the	fundamental concep	ts of mixed	-signal circ	uit design;		
Course Outcomes	CO# conc CO# CO# CO# perfe	CO#1: Analyze and differential amplifiers CO#2: Understand the design methodology for mixed signal IC design using gm/s concept. CO#3: Understand various compensation schemes used in opamp CO#4: Design the CMOS opamp and based on given specification CO#5: Appreciate the fundamentals of data converters and also optimized the performances CO#6: Able to design mixed-signal building blocks like comparators and PLL.						
Topics Covered/ Syllabus Module-I: (L – 04) High performance CMOS operational transconductance amplifiers analysis. Operation fully differential amplifiers, Types of common mode feedback circuits, Gilbert Cell. Module-II: (L – 05) Introduction to gm/Id technique and Design method using gm/Id technique. Generation gm/ID, gm/gds, ft plots using CAD tools. Design of amplifiers using gm/Id technique.					l. ration o			
	Mod Freq Com Com	dule-III: (L – juency compapensation, inpensation.	- 05) pensation schemes: Miller Compensa	Dominant-	Pole Comp		hunt-Capa	
Module-IV: $(L-06)$ Switched capacitor circuits, design of switched capacitor amplifiers and integrators, of opamp finite gain, bandwidth and offset, circuit techniques for reducing effects opamp imperfections, switches and charge injection and clock feed-through effects.					ffects o			
		lule-V: (L – 6 ign of sample	06) and holds and comp	arators.				
Module-VI: $(L-06)$ Fundamentals of data converters; Nyquist rate A/D converters (Flash, interpolating, fold flash, SAR and pipelined architectures); Nyquist rate D/A converters - voltage, current charge mode converters; Oversampled A/D and D/A converters.								
Module-VII: $(L-08)$ Basic PLL topology, dynamics of simple PLL, phase detectors, Phase frequency det Loop filters, Charge Pump PLLs, Ring Oscillator, VCO.						tector,		

Text Books, and/or Reference	Text Books: 4. Design of Analog CMOS Integrated Circuits, by Behzad Razavi, McGraw-Hill 1. R. Gregorian - Introduction to CMOS Opamps and Comparators. Wiley
material	Reference: 1. T. Carusone, D. Johns and K. Martin - Analog integrated circuit Design

EC 9041: Mixed Signal IC Design (Elective)
[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Analyze and differential amplifiers.	2	1	3	1	1	1
CO 2	Understand the design methodology for mixed signal IC design using gm/Id concept.	1	1	3	2	1	1
CO 3	Understand various compensation schemes used in opamp.	1	1	3	2	1	1
CO 4	Design the CMOS opamp and based on given specification.	2	2	3	3	2	1
CO 5	Appreciate the fundamentals of data converters and also optimized their performances.	2	2	3	2	2	1
CO 6	Able to design mixed-signal building blocks like comparators and PLL.	3	3	3	2	3	1
Average			1.67	3	2	1.67	1

		Department of	Electronics and	Communi	cation Eng	gineering					
Course	Ti	tle of the course	Program Core	Total Nu	mber of cor	tact hours: 4	0	Credit			
Code			(PCR)/	Lecture	Tutorial	Practical	Total				
			Electives (PEL)	(L)	(T)	(P)	Hours				
	Lo	ow Power									
EC9042	Ci	rcuits and	PEL	4	0	0	4	4			
	Systems										
				Course Assessment methods: (Continuous (CT), Mid-semester							
Pre-requisite	es:		assessment (MA) and end assessment (EA)):								
EC1013: Digit Design.	tal an	d Analog IC	Assignments, (Quiz, Mid-so	emester Exa Examination		nd End Sei	nester			
Course			ı als with issues an								
Objectives				ng fundamentals of power dissipation, leakage mechanisms and er techniques in a CMOS digital circuit.							
Course			e knowledge of t	knowledge of the fundamentals and applications of Low-power							
Outcomes	Outcomes CO#2: Identification circuits. CO#3: Analyminimize/optim CO#4: Learn and circuit level CO#5: Design		rarious leakage/ switching power reduction mechanisms at device level								
Syllabus/To Covered	pics	Total Lecture h Module-I:(L – 0									
		Introduction: Need for Low power VLSI chips - Low Power Design Methodology - Logic synthesis for Low power.									
	Source		L- 04) wer dissipation in CMOS circuits: static power dissipation-diode leakage reshold leakage power, gate and other tunnel currents; dynamic power hort circuit power, switching power, Glitching power; degrees of freedom.								
Correlation Ana Techniques - Es		s and Estimation: Gate level Analysis, Architecture level Analysis, Data alysis, Monte-Carlo Simulation, Probabilistic Power Analysis. Statistical stimation of Glitching Power - Sensitivity Analysis - Circuit Reliability - ion at the circuit level - High level Power Estimation - Estimation of									
transistors- Tran threshold voltage transistors, varia run time leaka		– 08) Optimization Technolisistor Leakage Mes, various approach ble threshold voltage power- multiparious issues related	lechanism, hes for the ge CMOS (ble-threshol- to power g	Leakage (fabrication VTCMOS).d voltage	Current Estimof multiple transistor transist	mation. Nathreshold acking ap	Multiple voltage proach, gating				

power management techniques, dual- V_t technique, delay and energy constrained dual- V_t techniques.

Module-IV: (L-08)

Dynamic Power Optimization Techniques: Supply voltage scaling approaches: parallelism, pipelining, using multiple supply voltage, module level voltage selection, clustered voltage scaling, level converters, multiple supplies inside a block, supply voltage limitations, Optimum supply voltage, multi-level voltage scaling (MVS), dynamic voltage and frequency scaling (DVFS), adaptive voltage scaling (AVS), System level approach- hardware/software co-design, encoding techniques, clock gating, gated clock finite state machines (FSMs), pre-computational logic, basic approach of minimizing glitching power, Dynamic CMOS and Pass-transistor logic styles.

Module-V: (L-04)

Low Power Static RAM Architectures: Organization, MOS Static RAM Memory Cell, Banked Organization, Voltage Swing Reduction, Power Reduction.

Module-VI: (L-04)

Low Voltage CMOS VLSI Technology: BICMOS and Silicon On Insulator (SOI) Technology. Recent Trends in low power VLSI Designs & its research issues in industry.

Text / Ref.

Text Books:

Books

- 1. Anantha P Chandrakasan and Robert W Brodersen, "Low Power Digital CMOS Design", Kluwer Academic Publishers, Holland, 1995.
- 2. Ajit Pal, "Low Power VLSI Circuits and Systems", Springer, 2015.

References:

- 1. Gary B Yeap K, "Practical Low Power Digital VLSI Design", Kluwer Academic Publishers, 1998.
- 2. Kuo J B and Lou J H, "Low Voltage CMOS VLSI Circuits", John Wiley and Sons, Singapore, 1999.
- 3. Kaushik Roy and Sharat C Prasad, "Low Power CMOS VLSI circuit Design", John Wiley and Sons, 2000.

EC 9042: Low Power Circuits and Systems (Elective)[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Acquire knowledge of the fundamentals and applications of Low-power circuits	2	1	2	2	1	1
CO 2	Identify various leakage/ switching power sources in a MOSFET and a digital circuits.	3	1	3	3	3	1
CO 3	Analyze the various issues to power dissipation and techniques to minimize/optimize	3	2	3	3	3	1
CO 4	Learn various leakage/ switching power reduction mechanisms at device level and circuit level.	3	2	3	2	2	1
CO 5	Design and implementation of a power-aware circuits and systems	2	1	2	3	3	2
CO 6	Evaluate the performance of low power circuits and systems	2	1	2	3	3	2
Average		2.50	1.33	2.50	2.67	2.50	1.33

	Departmen	t of Electronics and G	Communica	tion Engine	ering					
Course	Title of the course	Program Core								
Code		(PCR) /	Lecture	Total	Credit					
0000		Electives (PEL)	(L)	Tutorial (T)	Practical (P)	Hours				
EC9044	RF IC Design	PEL	4	0	0	4	4			
		(Open Elective)								
Pre-requis	ites / Co-requisites	Course Assessment methods: (Continuous (CT), Mid-semester								
		assessment (MA) and end assessment (EA)):								
Communication Theory, Signals and Systems, Analog IC Design		Assignments, Quiz, Mid-semester Examination and End Semester								
and byster	ns, maiog ie besign	Examination								
Course		f the course is to								
Objective		integrated circuits de			cusses metho	ds and te	chniques			
		design oriented to Cl								
Course		various architectures	•	•			ers			
Outcomes		and design basic RF b								
		d optimize RF blocks								
		sic RF measurement	s parameter	s such as S-	parameters,	sensitivity	, noise			
	figure, IIP3				_					
	CO#5:Appreciate	e the different LNA t	the different LNA topologies & design techniques							
Topics	Total Lecture he	ours: 40								
Covered/	Total Ecctare in	5415. 10								
Syllabus	Module-I: (L – (Module-I: (L – 06)								
2 Jilue us	,	Basic Concepts in RF Design, Architectures, Transmission media and Reflections,								
	_	transfer, Scattering		,			,			
	Module-II: (L –	,								
		ologies (CMOS, Si-Ge, SoI), fundamental limitation of speed & gain of ous technologies								
	transistors in vari	ous technologies								
	Module-III: (L -	- 06)								
	•	Different Noise Mechanisms: Classical two-port noise theory, noise models for active and								
		passive components								
		Module-IV: (L – 06)								
		Low Noise Amplifiers: SNR, LNA topologies, power constrained noise optimization,								
		linearity and large signal performance. Linearity consderations,1-dB compression, IIP, THD estimation.								
	THD estimation.									
	Module-V: (L –	04)								
	*	tive Mixers: multiplier-based mixers, sub-sampling mixers, diode-ring								
	mixers.									
	Module-VI: (L -	·					_			
		RF Passive Components: Characteristics of passive IC components at RF frequencies –								
	interconnects, res	interconnects, resistors, capacitors, inductors and transformers – Transmission lines.								
	Modulo-VIII (1	Module-VII: (L – 04)								
		Oscillators: Basic Principles, Cross-Coupled VCO, Phase Noise								
	Oscillators, Dasit	. i illicipies, cioss-c	oupled VC	o, i mase in	,150					
	Module-VIII: (I	(2.04)								
		RF power amplifiers – Class A, AB, B, C, D, E and F amplifiers, modulation of power								

	amplifiers, linearity considerations.
Text Books,	Text Books: 1. RF Microelectronics, Behzad Razavi, Prentice Hall of India (2001) 2. VLSI for Wireless Communication, Bosco Leung, Springer (2011)
Reference material	Reference: 1. Thomas H. Lee, The Design of CMOS Radio Frequency Integrated Circuits, Cambridge University Press.

EC 9044: RF IC Design (Elective)
[Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Analyze various architectures of today's digital radio transmitters and receivers	2	1	2	2	1	1
CO 2	Describe various basic RF building-blocks in CMOS technology	3	1	3	3	3	1
CO 3	Choose and optimize RF blocks (circuits) using CAD tools	3	2	3	3	3	1
CO 4	Define basic RF measurements parameters such as S- parameters, sensitivity, noise figure, IIP3	3	2	3	2	2	1
CO 5	Select appropriate LNA/Mixer/Oscillator topologies & design them	2	1	2	3	3	2
	Average		1.33	2.50	2.67	2.50	1.33

	Departmen	t of Electronics and	Communica	tion Engine	eering				
Course	Title of the course	Program Core	Total Nu	mber of cor	ntact hours: 4	0	Credit		
Code		(PCR) /	Lecture	Tutorial	Practical	Total			
		Electives (PEL)	(L)	(T)	(P)	Hours			
EC9046	FPGA based	PEL	4	0	0	4	4		
	Design								
Pre-requis	Pre-requisites Course Assess			ent methods (Continuous (CT) and end assessment					
	(EA))								
Boolean al	lgebra, Logic design	Assignments, Qui	z, Mid-semester Examination and End Semester						
fundament	tals	Examination							
Course	CO1: Explain lo	gic synthesis technic	ques – two	level and m	nultilevel syn	thesis.			
Outcomes	CO2: Design sys	tems using FPGAs a	nd CPLDs.						
	CO3: Design se	quential machine de	sign using I	FPGAs.					
CO4: Design systems for low power operation.									
Topics	Topics Total Lecture hours: 40								
Covered									

Module-I: (L-05)

Logic design fundamentals: Two level synthesis – SOP/POS forms, Logic minimization, Limitations of two level synthesis, introduction to multi-level synthesis.

Module-II: (L-05)

Programmable Logic Devices: Programmable Logic Array (PLA) architecture; Programmable Array Logic (PAL), PAL vs. PROM, Fan-in expansion feature, Architecture for sequential circuit implementation, Typical PAL chips; Complex Programmable Logic Devices (CPLD).

Module-III: (L-07)

Programmable Gate Arrays: Gate Array concept, Mask programmable and Field Programmable Gate Arrays; Look up tables (LUT) Configurable logic blocks (CLB), logic design using LUT's; Multi-level synthesis techniques — Factoring and Functional decomposition, Shannon's Expansion Theorem; Generalized FPGA Architecture.

Module-IV: (L-06)

Sequential Circuit Design: Finite State Machines, Moore and Mealy Machines; State diagrams, State table, State assignment, derivation of next-state and output expressions, state minimization; State assignment for low power operation; CAD tools for FSM synthesis.

Module-V: (L-04)

Advanced features of modern FPGAs: Block RAMs, Embedded processor, Communication ports, Analog interface.

Module-VI: (L-06)

Typical case studies: Simple logic functions — Decoder, encoder, multiplexer, demultiplexer, BCD to seven-segment decoder, keyboard/display interface; memory elements and arrays; sequential machine design — sequence generators, timing generators, a typical machine design (example: vending machine); A simple CPU design.

Module-VII: (L-04)

Design analysis: Static timing analysis, Power analysis, Resource utilization, noise, clock network, DRC, debugging methods.

Module-VIII: (L-04)

FPGA as a Hardware Debugging platform: Hardware troubleshooting methods, Looking into the chip – Logic State Analyzer and its use; Concept of Hardware emulation – simulation vs. Emulation, FPGA as a Hardware emulator, Break-points and their utility,

	setting break-points in FPGA based design.
Text Books, and/or reference material	Text Books: 1. Fundamentals of Digital Logic with Verilog Design by S. Brown and Z. Vranesic (McGraw Hill.)
	Reference Books: 1. A Verilog HDL Primer by J. Bhasker (B.S. Publications)

EC 9046: FPGA Based Design (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Learn logic synthesis techniques – two level and multilevel synthesis.	2	1	2	2	1	1
CO 2	Be able to design systems using FPGAs and CPLDs.	3	1	3	3	3	1
CO 3	Learn sequential machine design using FPGAs.	3	2	3	3	3	1
CO 4	Learn to design systems for low power operation.	3	2	3	2	2	1
	Average	2.75	1.5	2.75	2.5	2.25	1

	Depart	ment of Electronics and	Communica	tion Engine	eering			
Course	Title of the cours	e Program Core	Total Nu	mber of cor	ntact hours: 4	0	Credit	
Code		(PCR) /	Lecture	Tutorial	Practical	Total		
		Electives (PEL)	(L)	(T)	(P)	Hours		
EC9047	MEMS &	PEL	4	0	0	4	4	
	Microsystems							
	Technology							
Pre-requis	ites	Course Assessment (EA))	nt methods ((Continuous	s (CT) and er	nd assessm	nent	
NIL		Assignments, Qui Examination	z, Mid-sem	ester Exami	nation and I	End Semes	ster	
Course	Develop fund	lamental concepts of ME	EMS system	n, MEMS d	evice modeli	ng technic	ues and	
Objectives	learn MEMS	device fabrication proce	ess and MEN	MS device p	ackaging			
	CO#1: Unde	rstand characteristics of	MEMS sy	stem				
Course		rstand basic building bloom						
Outcomes		qualitative and quant	itative anal	ysis technic	ques in genera	al MEMS	systems	
		n techniques in MEMS						
		tigate complex designs						
	CO#6: Unde	rstand synthesis and fal	brication of	MEMS sys	stem			
Topics Covered	Total Lectur	re hours: 40						
	Module-1: (. – 06)						
	-	e fabrication process						
	Module-2: (
			g, Statics, Dynamics, Quasi static analysis, Energy Methods					
	Module-3: (I Elasticity, St		ures, Thermal Energy Domain, Fluids, Electronics					
	Module-4:(L		,	,				
		se, Feedback systems						
	Module-5:(L	=						
	Integration o	MEMS systems, Scalin	ig effect, Re	liability of	MEMS devic	ces		
	Module-6:(L Case studies	=						
		III MEMS.						
Text Book and/or		em Design by Stephen I	D. Senturia,	Springer				
reference	Reference B		,	1 0				
material	1. Micro and	Smart Systemsby K.J. Vasuresh, Wiley	Vinoy, S. G	opalakrishn	an, K.N. Bha	nt, V.K. A	atre	

EC 9047: MEMS and Microsystems Technology (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Understand characteristics of MEMS system	2	1	3	1	1	1
CO 2	Understand basic building blocks of general MEMS systems	1	1	3	2	1	1
CO 3	Apply qualitative and quantitative analysis techniques in general MEMS systems	1	1	3	2	1	1
CO 4	Design techniques in MEMS	2	2	3	3	2	1
CO 5	Investigate complex designs in MEMS systems	2	2	3	2	2	1
CO 6	Understand synthesis and fabrication of MEMS system	3	3	3	2	3	1
	Average	1.83	1.67	3	2	1.67	1

	Department o	f Electronics and	Communi	cation Engi	neering				
Course	Title of the course	Program	Total Nu	mber of con	tact hours: 4	0	Credit		
Code		Core (PCR) /	Lecture	Tutorial	Practical	Total			
		Electives	(L)	(T)	(P)	Hours			
		(PEL)							
EC9049	Nanoelectronics	PEL	4	0	0	4	4		
Pre-requisite:	s:	Course Assess	Course Assessment methods (Continuous (CT) and end assessment						
		(EA))							
Microelectron		Assignments,	Quiz, Mid-s	emester Exa	mination an	d End Sen	nester		
Semiconducto (Solid State D	or Device Physics Devices)	Examination							
	,								
Course	*	state of art in the		emiconducto	or device ph	ysics and	materials		
Objectives		nable the Nano-E		MOS taaba	alogy and th	a icena i	n gooling		
	· ·	fundamentals of a sub-100nm region			nogy and u	ie issue ii	1 scanng		
	Emerging stud	ies for need of ne	on-classical		with new de	evice struc	cture and		
	nanomaterials v	will be elucidated.							
Course	CO#1 • Demo	nstrate understai	nding of	fundamenta	l of nanod	evices fa	hrication		
Outcomes	techniques								
Outcomes	CO#2: Demon	strate understand	ing of nano	technology	concepts for	device fa	brication		
	CO#3: To qui	re fundamental u	nderstandin	g for electr	onics and op	ptical prop	perties of		
	nanomaterials.	equire knowledg	e of basic	nanodevic	ce nrincinle	s and fa	brication		
		various nanoscale		nanodevi	ee principle	s and ra	oricution		
Syllabus/Top	ics Total Lecture	hours: 40							
Covered	Total Lecture	nouis. 40							
Covered	Module-I: (L -								
		o nanotechnology nethod (top-dow		e of things bottom-up),	-	f nanotec applicat			
	nanotechnology	` .	ii and i	oottom-up),	cincignig	аррпсас	ions or		
	Module-II: (L	_ 10)							
	Electronic and	Optical proper							
		vo –dimensional a ballistic condu							
		onant tunneling, C		_	-				
	Module-III: (I	. – 10)							
	Nanotechnolog	y: Deposition tecl	_				-		
		chniques, Nanon nostructure Surfa							

	Atomic Force Microscope (AFM), Scanning Tunneling Microscope and scanning near field optical microscope.
	Module-IV: (L – 10) Shrink-down approaches: Electronic devices Based on Nanostructures: Advance Heterostructure Devices, Downscaling of the MOSFET. Nanoscale FET Transistors, the Ballistic FET, Resonant Tunneling Devices and Circuits, Single Electron Transistor and Related Devices. Devices based on carbon nanotubes, Spintronic Devices; Optoelectronic Devices using Nanostructures: Quantum well and Quantum Dot LASERS, Quantum Cascade LASER, Quantum well-infrared photodetector, Superlattice LASER.
Text / Ref.	Text Books:
Books	 Introduction to Nanotechnology, C.P. Poole Jr., F.J. Owens, Wiley (2003). Nanoelectronics and Information Technology (Advanced Electronic Materials and Novel Devices), Waser Ranier, Wiley-VCH (2003).
	References:
	1. Nanosystems, K.E. Drexler, Wiley (1992)
	2. The Physics of Low-Dimensional Semiconductors, John H. Davies, Cambridge University Press, 1998.
	3. Fundamentals of Modern VLSI Devices, Y. Taur and T. Ning, Cambridge University Press.
	4. Karl Goser, "Nanoelectronics and Nanosystems," Springer, 2004

EC 9049: Nanoelectronics (Elective)[Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Demonstrate understanding of fundamental of nanodevices fabrication techniques	2	1	2	2	1	1
CO 2	Demonstrate understanding of nanotechnology concepts for device fabrication and characterization.	3	1	3	3	3	1
CO 3	To quire fundamental understanding for electronics and optical properties of nanomaterials.	3	2	3	3	3	1
CO 4	To acquire knowledge of basic nanodevice principles and fabrication approaches for various nanoscale devices.	3	2	3	2	2	1
	Average	2.75	1.5	2.75	2.5	2.25	1

	Depa	artment of Elec	tronics and C	ommunic	ation Engi	ineering		
Course Code	Title o	f the course	Program	Total Nu	mber of co	ntact hours:	40	Credit
			Core (PCR)	Lecture	Tutorial	Practical	Total	
			/ Electives	(L)	(T)	(P)	Hours	
			(PEL)					
EC9051	Testin	g and	PEL	4	0	0	4	4
	Verification of VLSI							
	Circui	its						
Pre-requisites:			Course Assess	sment meth	l nods: (Conti	nuous (CT).	, Mid-sem	ester
			assessment (M	(IA) and en	d assessmer	nt (EA)):		
Digital Design.			Assignments,	Quiz, Mid-	-semester E	xamination	and End	
			Semester Exa	mination				
Course Object	ives	To expose the	students, the b	asics of te	sting and v	erification t	echniques	for the
		digital IC desig	gn.					
Syllabus/Topic Covered	es	CO#2: Generate CO#3: Demons CO#4: Discuss CO#5: Use mod Total Lecture I Module-I: (L — Physicalfaultsan Fault simulation Module-II: (L Test generation Podem, random aliasing and its of Module-III: (L PLA testing: cro Module-IV: (L Memory testing generation. Module-V: (L— Delay faults and types.	about Built-in-Sidern tools for test tools for test tools for test tools for test tools. 05) adtheirmodeling to parallel, deduction for combination etc. Exhaustive effect on fault combinations. - 05) ass-point fault manual for tools. - 05) ag: permanent,	t of Memor self Test and sting and ver- all. Faultequive trive and contact at a contact we, random overage.	ry testing tend its application. ralenceandd oncurrent tend cuits: Boom and weign generation, of the control o	ominance; fachniques; cr lean differ thted test po-	ault contical pathence,D-allattern gen	llapsing, ntracing. gorithm, neration;
		-	- 05)	-				
		scan path and L	SSD, boundary	scan.				

	-
	$\label{eq:module-VII:} \begin{tabular}{ll} \textbf{Module-VII:} (L-05) \\ \textbf{Built-in self-test techniques: LBIST and MBIST. Verification: logic level (combinational and sequential circuits), RTL-level (data path and control path). \\ \textbf{Verification of embedded systems. Use of formal techniques: decision diagrams, logic-based approaches.} \end{tabular}$
	Module-VIII: (L – 05) ASIC/IP Verification, direct and random testing, Error detection and correction codes.
Text / Ref. Books	Text Books: 1. Essentials of Electronic Testing, M. L. Bushnell and V. D. Agrawal,3rd Kluwer Academic Publishers 2002
	References:
	Delay Fault Testing for VLSI Circuits, A. Krstic and K-T Cheng, 3rd Kluwer Academic Publishers. 2003
	2. Testing of Digital Systems, N. K. Jha and S. Gupta, 2nd, Cambridge University Press. 2003
	3. Digital Systems Testing and Testable Design, M. Abramovici, M. A. Breuer and A. D. Friedman, 3rd, Wiley-IEEE Press. 1994
	4. Fault Tolerant and Fault Testable P. K. Lala, 4th, Hardware Design, Prentice-Hall. 1986

EC 9051: Testing and Verification of VLSI Circuits (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Extend knowledge of the requirement of fault modeling in VLSI circuits.	1	1	1	2	1	1
CO 2	Generate test vectors to test a circuit efficiently covering maximum faults.	2	2	3	2	1	1
CO 3	Introduce students to the concepts Memory testing techniques.	2	2	2	3	2	1
CO 4	Understanding Built-in-Self Test and its application in modern digital design	2	2	3	2	2	1
CO 5	Use modern tools for testing and verification.	2	2	3	3	2	2
	Average	1.8	1.8	2.4	2.4	1.6	1.2

	Departmen	t of Electronics and	Communica	tion Engine	eering		
Course	Title of the course	Program Core	Total Nu	mber of cor	ntact hours: 4	-0	Credit
Code		(PCR) /	Lecture	Tutorial	Practical	Total	
		Electives (PEL)	(L)	(T)	(P)	Hours	
EC9030	Artificial	PEL	4	0	0	4	4
	Intelligence and						
	Soft Computing						
Pre-requisi		Course Assessmen	nt methods	Class test/a	assignment, N	Mid-semes	ter and
•		End assessment (I		`	,		
NIL		CT+MA+EA	,,				
Course	CO1. Basics of o	pptimization and soft	computing	algorithms			
Outcomes		erent soft computing		argoriumis			
Outcomes		icial neural network	•	ino			
		idial basis function n					
		nachine learning algo					
Topics	Total Lecture he		Titiliis and	crastering			
Covered	Total Dectare in	ouis. To					
2010100							
	Module-I: (L – 0	,					
		ptimization, Constra			•		
		sed on soft compu			ms, Quantu	m particle	e swarm
	optimization, Wh	nale optimization, Cr	ow search a	lgorithm			
		07)					
	Module-II: (L –		1	1	· · · · · · · · · · · · · · · · · · ·		1.1
		on algorithm,Teachin	ig learning i	oased optin	nization, Sine	e cosine al	gorithm,
	Moth flame optir	nization					
	Module-III: (L -	-06)					
	I	earch optimization	Algorithm	Particle	ewarm ont	imization	Firefly
	algorithm	aren optimization	Aigoriumi,	, I articic	swarm opt	iiiizatioii,	Theny
	argoriumi						
	Module-IV: (L -	- 07)					
	`	artificial neural	network.Si	upervised	Learning N	Neural N	etworks.
		dline, Multilayer feed					
		pagation algorithm,					
	technique	(8			6	1 8
	1						
	Module-V: (L –	07)					
		nction Neural Netv	vorks(RBF)	Training o	of RBF usin	ig pseudo	inverse
		clustering using K-m		Č			
	Module-VI: (L –	- 06)					
		g machine(ELM),Ker	nel based E	LM, Rando	m vector fur	nctional lir	nk neural
		Training and testing	of ELM and	1 RVFL,CN	IN		
Text Book	· · · · · · · · · · · · · · · · · · ·						
and/or	_	oft Computing, S N S				•	
reference		proach to Soft Comp					n
material		rks: A Classroom Ap	proach, 1/e	by Kumar S	Satish, McGra	aw Hill	
	Reference Book						
	· ·	n and G.A.V.Pai, Net	ural Networ	ks, Fuzzy L	ogic and Ger	netic Algo	rithms,
	PHI						
		and Soft computing,					
		orks: A Comprehensi	ve Foundati	on (2 nd Edi	tion), Simon	Haykin, P	rentice
	Hall.						

EC 9030: Artificial Intelligence and Soft Computing (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Basics of optimization and soft computing algorithms.	1	1	1	2	1	1
CO 2	Learn different soft computing algorithms.	2	2	3	2	1	1
CO 3	Learn artificial neural network and its training.	2	2	2	3	2	1
CO 4	Study of radial basis function neural and its training.	2	2	3	2	2	1
CO 5	Study of machine learning algorithms and clustering.	2	2	3	3	2	2
	Average	1.8	1.8	2.4	2.4	1.6	1.2

	De	partment of Elect	ronics and	Communicat	ion Engineer	ing		
Course	Title of the	Program	Total Nu	mber of con	tact hours: 40)	Credit	
Code	course	Core	Lecture	Tutorial	Practical	Total]	
		(PCR)/	(L)	(T)	(P)	Hours		
		Electives						
		(PEL)						
EC 9013	Optical	PEL	4	0	0	4	4	
	Communicati		gaggmant m	nothoda (Clar	 ss test/assignr	nont Mid a	amastar and	
Pre	e-requisites:		sment (EA)		ss test/assigiii	nent, mu-s	emester and	
Electronic		and CT+MA+	EA					
	ectromagnetic fie							
Communica	nalog and Dig	ital						
Course		udents will be a	ble to lea	rn the intric	racies of des	ion constr	nints at ontical	
Outcomes		equency.	iore to real	in the mare	deres of dec	ngn consuc	ants at optical	
0.0000000000000000000000000000000000000		ne basic training	for underst	anding circu	its and syste	m level im	olementation in	
		tht wave technolog		C	•	•		
	CO3: Th	ne students can de	esign compo	onents and c	hoose approp	riate source	es and receivers	
	fo	r an optical netwo	ork.					
		nderstanding the u	isage of OT	DR in monit	toring an opti	cal commur	nication system.	
Topics	Total Lec	ture hours: 40						
Covered	Module-I	(1 - 02)						
	Introduction	on to optical communication; Shanno			-		_	
	representati	ber: Classification on and wave optics	-08) Classification of Fibers, Fiber materials and fabrication methods, Ray optics and wave optics representation for step index and graded index fibers, Modes, Phase ity, Power flow in step index fibers.					
	Propagation classification	II: $(L-06)$ on Characteristics on and effect of dis- r, isolator, circulato	persion in ir	nformation tra	•			
	Design asp analog fibe	communication sy	(1.500) of optical communication: optical fiber systems, modulation schemes, digital and amunication system, system design consideration, emitter and detector design, fiber rs, various amplifiers and its characteristics; OTDR					
	Module-V Optical transmitter	ansmitter: Basic o	2) :: Basic concepts, characteristics of semiconductor injection LASER, LED,					
	photo dete application practical c detection, s	T: $(L-06)$ ceiver: Basic concector, receiver designates; Direct detection onsiderations, modingle and multicarries.	gn, receiven; Coherent dulation and	r noise, rece communicat d demodulati	iver sensitivity ion: Basic co on schemes,	y, optical a oncept, detec	mplifier and its etion principles,	
	ivioauie- V	II: $(L - 04)$						

	Wavelength division multiplexing (WDM): multiplexing techniques, topologies and architectures, wavelength shifting, WDM demultiplexer, optical add/drop multiplexers.
	Module-VIII: $(L-04)$ Dense wavelength division multiplexing (DWDM): system considerations, multiplexers and demultiplexers; Fiber amplifier for DWDM, SONET/SDH transmission, modulation formats, NRZ and RZ signaling, DPSK system modeling. Potential applications and future prospects of optical fibers, multimode intensity sensors and single mode, Interferometric sensors. Recent trends in optical communication.
Text Books,	Text Books:
and/or	[1] J. M. Senior, "Optical Fiber Communications", PHI, 2nd Ed.
reference	[2] G. Keiser, "Optical Fiber Communication", McGraw Hill, 3rd Ed.
material	[3] Ghatak &Thyagarajan, "Introduction to fiber Optics", Cambridge University press.
	[4] Henry Zanger and Cynthia Zanger, Fiber Optics Communication and Other
	Application, Macmillan Publishing Company, Singapore 1991.
	Reference Books:
	[1] J.H. Franz & V.K.Jain, "Optical Communications", Narosa Publishing House.
	[2] Ghatak & Thyagarajan, "Contemporary Optics", Series Title: Optical Physics and
	Engineering, Springer
	[3] Amnon Yariv and Pochi Yeh, Photonics: Optical electronics for Modern
	Communication, 6 th Ed., New York, Oxford University Press

EC 9013: Optical Communication [Mapping between course outcomes (COs) and program outcomes (POs)]

CO	Statement		1	Program	Outcom	ies	
CO	Statement	PO1	PO2	PO3	PSO1	PSO2	PSO3
CO1	Students will be able to learn the intricacies of design constraints at optical frequency.	1	1	2	2	3	1
CO2	The basic training for understanding circuits and system level implementation in lightwave technology.	3	2	3	2	1	2
CO3	The students can design components and choose appropriate sources and receivers for an optical network.	2	1	3	1	2	1
CO4	Understanding the usage of OTDR in monitoring an optical communication system.	2	2	3	2	2	2

	Department of	of Electronics and C	Communica	tion Engine	ering			
Course	Title of the course	Program Core	Total Nu	mber of cor	ntact hours: 4	-3	Credit	
Code		(PCR) /	Lecture	Practical	Total			
		Electives	(L)	(T)	(P)	Hours		
		(PEL)						
	Queuing Theory	PEL	4	0	0	4	4	
EC 9014	for	(Program						
	Telecommunication	Elective)						
Pre-requisi	tes	Course Assessment methods (Class test/assignment, Mid-semester						
_		and End assessment (EA))						
Communicat	ion Networks,	CT+MA+EA						
Engineering 1	Mathematics							
Course	CO#1: Identify standa	ard queuing networks.						
Outcomes	CO#2: Integrate trans	portation and mate	rial handlin	g topics wit	h the general	l queuir	ng	
	models.							
	CO#3: Analyze case st	tudies to indicate b	readth and o	depth of que	euing system	s and their	r range	
	of applicability.							
	CO#4: Interpret softw	are programs for d	lemonstratio	on and solut	ion of topolo	ogical netv	vork	
	design.							
Topics	Total Lecture hours:	43				•		
Covered								
	Module I: (L. 04)							

Module I: (L- 04)

Problem Overview: Introduction to stochastic process, Evolution of queuing and queuing network models and their optimization for traffic congestion and performance.

Module II: (L-06)

Mathematical Models and Properties of Queues: Modelling of infinite and finite buffer queuing networks especially analysing four categories of queuing networks (Product Form, Non-Product Form, Blocking, Transportation and Loss queues).

Module I: (L-07)

Transportation and Loss Queues: State dependent M/G/c/c queues and queuing network models incorporating micro and macro aspects of traffic flow to capture throughput volume, speeds, density and congestion in transportation systems.

Module III: (L- 07)

Open Queuing Network Algorithms: Topological network design and computer implementation for performance and optimization of Product Form (Jackson) network, Non-Product Form networks (queuing network approximation algorithm of Whitt), Blocking networks (Expansion method for exponential blocking, generalized expansion method for more general distributions).

Module IV: (L-08)

Closed Queuing Network Performance Models: Product Form networks (Gordon and Newell algorithms), Non-Product Form networks through generalized service time distributions, closed queuing analysis of Blocking networks, movement of goods from one queue to another in closed transportation and loss networks.

Module V: (L-08)

Optimal Resource Allocation Problems in Topological Network Design: Resource allocation problems in improving stochastic flow process, Accessibility and egress addressed

	optimal routing optimization in design of queues, Optimal topology problems examined through integer and non-linear programming aspects (fixed and spatially generated topology).
Text	Text Book:
Books,	[T1]. Introduction to Queuing Networks, Theory and Practice – Smith, J. MacGregor (Springer).
and/or	Reference Book:
reference	[R1]. Data Networks – D. Bertsekas and R. Gallager (Prentice Hall).
material	

		Den	artment	of Electr	onics and	Commun	ication Eng	ineering	
Course	Title of		Progran				ontact hours		Credit
Code	cours		(PCI		Lecture	Tutorial	Practical	Total Hours	
			Electives		(L)	(T)	(P)		
EC9018	Image Process	ing	PE		4	0	0	4	4
Prerequis		8		Course	Assessme	ent method	ls (Class test	/assignment, Mid	-semester
•					d assessm		`	,	
Signals ar	nd System	s, Di	gital	CT+M	A+EA				
Electronic	es, Digital	Sign	al						
Processin									
Course O	utcomes	CO CO in d	#2: Analy #3: Unde ligital ima	y ze digita rstand t ges.	al images t he applica	through mu tion of mo	ıltiresolution	on techniques. I techniques. processing and so	egmentation
Topics Co	overed		al Lectur			recognition	i teciniques.	•	
1		Mo Dig Res	dule I: (L ital Ima	04) ge Fur	ndamental			n, Sampling, Q transforms, Conv	
		Ima Ima Ima Ima Ima one Ima one	dule III: (age Restormation of filtering sence of the content of	nncemen ning and (L-05) ration: N noise or ng, Estir	smoothen Model of in the spatial mating the	mage degr filtering, degradation	ions (spatial adation, Noi Periodic no	rms, Histogram and frequency ba se models, Restor- bise reduction by Weiner filtering,	ration in the requency
		Mo Mu fund Ima	dule IV: (Iti-resolution, Water decoming the decoming dule V: (Inpression	(L-05) tion Im velet sen position L-04) and I	age Processies, Discression compa	cessing: Sete wavelet ression usi	hort time is transform a ng discrete v	Fourier transforr and multi-resoluti vavelet transform	on analysis,
Module V				(L-04) al Proce	essing: Dil	ation and	erosion, Ope	g adaptive compre	
detection, T				I: (L-06) mentation : Detection of discontinuities, Edge linking and boundary Thresholding, Region based segmentation, Segmentation by cal watersheds, Use of motion in segmentation.					
				Images nalysis,	Decision	tree and f		asics of features rchy, Scale invar	

Text Books, and /	Text Books:
or reference	1. Digital Image Processing: R C Gonzalez and R E Woods; Pearson
material	Education.
	2. Guide to Signals and Patterns in Image Processing- Foundations, Methods
	and Applications: Apurba Das; Springer.
	3. Digital Image Processing and Computer Vision: Sonka, Hlavac and Boyle;
	Cengage Learning (India Edition).
	Reference Books:
	1. Digital Image Processing: K R Castleman; Pearson Education.
	2. Digital Image Processing: S Sridhar; Oxford Higher Education.

	Depar	tment of Electro	onics and Com	munication E	ngineering			
Course	Title of the	Program Core	Total Numbe	r of contact ho	ours: 40		Credit	
Code	course	(PCR)/	Lecture (L)	Tutorial (T)	Practical (P)	Total	-	
		Electives (PEL)	` '	, ,		Hours		
	Satellite	PEL	4	0	0	4	4	
EC 9024	Communication							
Pre-requis	sites:		Course Assessi	ment methods	(Class test/assi	gnment,	Mid-	
1			semester and E		•	,		
	in Electromagne		CT+MA+EA					
•	olving capability (
	nalog and Digital (
and coding	y knowledge on inf	ormation theory						
Course	CO1: To com	pute the satellite	orbit paramete	rs. design orbi	ts and can be a	able to cl	assify them	
Outcomes		n Kepler's six ele	-	is, acsign of or	is and can be		assiry them	
Gutcomes		and the concept of		ching and posit	tioning of satel	lites in o	rbits	
		computations of 1		•	•			
	commu	•				- · F	F	
		ate the concept of	f multiple acces	sing technique	es in satellite co	ommunic	ation.	
		ability to classif	•	•				
Topics	Total Lecture							
Covered								
	Module I: (L-	02)						
	Historical bac	kground, Basic o	concepts, Frequency	iency allocation	on for satellite	services	s, orbital &	
	spacecraft pro	blems, comparis	on of network	s and services	s, modulation	technique	es used for	
	satellite comm	unication. Spectr	um Manageme	nt (2L)				
	manoeuvres, o	ody problem, orborbital transfer, and wered flight, Lau	nd orbital pertu	ırbations. Lau	nch Vehicles-	•		
	satellite link, r	L- 08) e, the basic RF l noise temperature tenuation model.	, Antenna temp	perature, overa	ıll system temp		· ·	
	Module VI: (L- 08) Satellite subsystems and satellite link design- Altitude and orbit control (AOC) SubsyTT&C, power system, spacecraft antenna, transponder, Friis transmission equation, G/T rate earth station.							
	_	ess- FDMA, TI		techniques,	comparison	of multi	ple access	
	Electromagnet	L- 06) of satellite in raic Radiation prince, Passive, ground	nciples, Atmos	pheric window	v, Indian satel		_	

Text Books,	Text Books
and/or	[1] Dennis Roddy, Satellite Communication, 4/e, McGraw Hill
reference	[2] Louis J. Ippolito, Jr. Satellite Communications Systems Engineering: Atmospheric Effects,
material	Satellite Link Design and System Performance, Second Edition.
	Reference Books
	[3] Recommendation ITU-R P.618-11, P Series Radio Wave Propagation.
	[4] Pratt and Bostian, Satellite Communication, 2/e, John Wiley and Sons.
	[5] Floyd F. Sabins, Remote Sensing: Principles and Interpretation, 3rd edition (August 1996),
	W H Freeman & Co.
	[6] Tri T Ha, Digital Satellite Communication, McGraw Hill

EC9024: Satellite Communication (Elective)
[Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement]	Program	Outcom	ies	
CO	Statement	PO1	PO2	PO3	PSO1	PSO2	PSO3
CO1	To compute the satellite orbit parameters, design orbits and can be able to classify them based on Kepler's six elements.	1	1	2	2	3	1
CO2	Understand the concept of satellite launching and positioning of satellites in orbits	3	2	3	2	1	2
CO3	Can do computations of link design and classify different losses in propagation for space communication.	2	1	3	1	2	1
CO4	Assimilate the concept of multiple accessing techniques in satellite communication.	2	2	3	2	2	2
CO5	Develop ability to classify different types of application of satellite communication.	1	3	2	2	1	3

Course	Course Title of the Program Core Total Number of contact hours: 40						Credit
Code	course	(PCR) /	Lecture	Tutorial	Practical	Total	1
		Electives (PEL)	(L)	(T)	(P)	Hours	
	Microwave	PEL	4	0	0	4	4
EC 9025	Circuits and						
Pre-requis	Techniques		Course Asses	emant matho	ds (Class test	t/accionmer	nt Mid
1 re-requis	sites.			End assessm		/assigninei	it, iviiu-
Knowledge	in Electromagnet		CT+MA+EA		(211)		
problem so	olving capability (s						
Theory),	Analog circui						
	ce to a prelimina	ary course of					
Course	engineering.	will be able to lear	n the intricac	ries of design	constraints a	t high from	
Outcomes		ic training for und					
		se and space applic				Toquon.	7100 101 001
		dents can design p	planar circui	ts and can p	provide reaso	ning for th	ne obtained
	results.						
Topics	Total Lecture h	ours: 40					
Covered	Module I: (02)						
	wave, Safety of behaviour of Lu high RF. Real components.[1][Module II: (L-Review of Tra Properties of Safety of Safety of Tra Properties of	natrix, Transmission line to matrix, Transmission line to matrix. Transmission line to matrix line line line line line line line line	ference in lonents. Minime elements heory. Conon matrix and the matrix and the mode and group; Introduction	High frequent aturization are as microwal cept of Scalatheir relation Resonators malysis, cut-cap velocity, n of circular	ncy and related design of Leve and mm ttering Materiships Rectangulated frequency, power transwaveguide; F	rix N-port ar Wavegu , propagation smission, Rectangular	r frequency imponents at anar circuit t networks- ide- design on constant, attenuation,
	Module IV: (L- 06) Planar Transmission lines and Resonators: Propagation characteristics, comparison for different characteristics of the above mentioned lines. strip line, micro-strip line, coplanar waveguide, Slot line-design consideration, Substrate integrated waveguide, non radiating dielectric guides, Design synthesis and analysis[1][2]						
	components and Bethe-hole cou dividers and cou	08) nents and their S I their S matrix repler, magic tee, haplers; design proceedsign, scaling and of	presentation: nybrid ring, edure of filte	Attenuators, circulators, r using insert	Phase shifte Isolators; de- tion loss meth	r, Direction sign of pla	nal coupler, anar power

Module VI: (L- 06)

	Microwave and mm wave devices and Application to switches and mixers: TED (Gunn diode) & Avalanche Transit Time (IMPATT) device, Schottky diode, PIN & applications; Microwave bipolar transistor, Microwave field effect transistor. [2]
	Module VII: (L-06) Microwave Amplifier Design: Basic consideration in the design of microwave amplifier-transistor S-parameter, Stability, matching network, noise figure; matching network design using lumped elements and L-Section. Design of LNA.[1][4]
	Module VIII: (L- 04) Microwave and mm wave measurement basics: VSWR meter, tunable detector, slotted line and probe detector, spectrum analyzer, network analyzer, measurement of VSWR – low, medium and high, measurement of power: low, medium and high, frequency measurement.[1][4]
Text Books, and/or reference material	 Text Books: [1] David. M. Pozar, <i>Microwave Engineering</i>, 2/e, 1998 (John Wiley & Sons). [2] R Ludwig and P Bretchko, <i>RF Circuit Design: Theory and Application</i>, Pearson Education, New Delhi [3] Samuel Y Liao, <i>Microwave Devices and Circuits</i>, 3/e, PHI. [4] Sisodia and Raghuvanshi, <i>Microwave Circuits and Passive Devices</i>, New Age International [5] G H Bryant, <i>Principles of microwave Measurement</i>, London: P. Peregrinus Ltd. on behalf of the Institution of Electrical Engineers, c1988
	Reference Books: [1] P A Rizzi, Microwave Engineering: Passive Circuits, 2000, PHI [2] R E Collin, Foundations of Microwave Engineering, John Wiley and Sons India Pvt. Ltd.

EC 9025: Microwave Circuits & Techniques (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Students will be able to learn the intricacies of design constraints at high frequency.	2	1	2	2	3	1
CO 2	The basic training for understanding circuit design at microwave frequencies for our Country's defense and space applications would be enriched.	2	3	1	1	3	1
CO 3	The students can design planar circuits and can provide reasoning for the obtained results.	3	2	1	1	3	1
	2.3	2.0	1.3	1.3	3.0	1.0	

		nt of Electronics and	_			0	G 11:			
Course Code	Title of the course	Program Core (PCR) /	Total Nu	Credit						
Code		Electives (PEL)/OEL	Lecture (L)	Tutorial (T)	Practical (P)	Total Hours				
EC9036	EMBEDDED SYSTEMS	PEL	4	0	0	4	4			
Pre-requi		Course Assessment ((Class test/a	ssignment, N	Mid-semes	ter and			
	ctronics, Mechanics	CT+MA+EA								
Course Outcomes CO#1: Understand concept of contemporary Embedded systems CO#2: Apply analysis techniques to physical systems CO#3: Understand case study in Embedded system CO#4: Design of Embedded systems										
Topics Covered	Total Lecture h									
	Introduction to	Module I: (L-02) Introduction to Embedded systems: Motivation based on applications of embedded systems, Basics of Embedded systems, functional blocks								
	embedded syste	08) mbedded system: Mems, Continuous Dysition of State Machi	ynamics, Di							
	Cyber physical	Module III: (L-04) Cyber physical system architecture and Industry 4.0, Background of Industry standards, Cyber physical system, IoT, Industry 3.0, Industry 4.0								
	Microcontrollers	Module IV: (L- 14) Microcontrollers, Sensors, Actuators, Basics of Microcontrollers, 8951, Arduino microcontroller development board, I/Os, Sensors, Actuators								
		Module V: (L- 06) Data networking, Data communication techniques, Internet, Ethernet, WiFi, Bluetooth and Cellular, LoRa								
	Module VI: (L-Case study in en	06) nbedded system, Cas	e study base	d on applica	ations					
Text Bool and/or reference material	 Introduction Ashford Le Principles of Industry 4.0 Data Comm 	n to Embedded Syste e, Sanjit Arun kuman of measurement syste the industrial interr nunications And Net and Research Articl	r Seshia ems. By Bent net of things, working (SIE	iley by Alasdai	ir Gilchrist	·	Edward			

EC 9036: Embedded Systems (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

со	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Understand concept of contemporary Embedded systems.	1	2	1	1	1	3
CO 2	Apply analysis techniques to physical systems.	2	1	2	2	1	3
CO 3	Understand case study in Embedded system.	2	1	2	1	2	3
CO 4	Design of Embedded systems.	1	2	1	1	1	3
Average		1.5	1.5	1.5	1.3	1.3	3.0

	Departmen	nt of Electronics and	Communica	ation Engine	eering				
Course	Title of the course	Program Core	Total Nu	Credit					
Code		(PCR)/	Lecture	Total	-				
		Electives (PEL)	(L)	Tutorial (T)	Practical (P)	Hours			
EC9038	Error Control Coding	PCR	4	0	0	4	4		
Pre-requi		Course Assessme	nt methods	(Class test/a	assignment, N	Mid-semes	ster and		
		End assessment (l	EA))						
	gebra, Probability,	CT+MA+EA							
	cation Engineering	des about different to			مانسم دماسانم				
Course Outcomes	=	CO2: Understand generator matrix, encoding and decoding of different codes							
Outcomes	eoz. chacista	CO2: Understand generator matrix, encoding and decoding of different codes.							
		CO3: Learn LDPC, BCH, RS and Turbo codes. CO4: Analyze and mitigate errors in channels.							
		•							
т :		iate between differen	it coding str	ategies.					
Topics Covered	Total Lecture h	ours: 40							
Covered	Module I. (I O	0)							
	Module I: (L-0		n Dina Ei-	ld Vastar 9	Space .				
	introduction to I	Linear Algebra: Grou	p, King, Fie	iu, vector s	space.				
	Module II: (L-	10)							
	· ·	,	or and Darit	v Choole M	otricos Duel	Codes D	acadina		
		lock Codes: Generate es of linear block cod		-	aurces, Duar	Coues, D	ecounig,		
	General properti	es of fillear block coc	ies, naiiiiii	ng Code.					
	Module III: (L-	.04)							
	,	lgebraic description,	Encoding a	nd Decodin	g of Cyclic c	odes			
	Cyclic Codes. A	igeoraic description,	Lifeouring a	na Decoun	g of Cyclic C	oues.			
	Module IV: (L-	03)							
	· ·	operties, Encoding a	nd Decodin	σ.					
	Berr codes.	operates, Encouring a	na Becoun	ρ,					
	Module V: (L-	01)							
		RS) Codes: Definitio	n. Decoding	of RS cod	es.				
		,	,	,					
	Module VI: (L-	07)							
		odes: Definition, E	Incoding T	rellis and	State repre	sentation,	Viterbi		
	decoding, Error		C		1	,			
		•							
	Module VII: (L	- 03)							
	· · · · · · · · · · · · · · · · · · ·	Definition, Construct	ion, Regula	r and irregu	ılar LDPC, E	Belief Prop	oagation,		
		Decoding, Iterative De	_	J	•	,	· - ·		
	Module VIII: (L- 03)								
	Turbo Codes: Definition, Construction methods, Decoding								
Text Book									
and/or		ontrol Coding; Funda			ns: Shu Lin	and Danie	l. J.		
reference	Costello	Jr. Second Edition, I	Pearson Ind	lia.					
material	2 Eggantia	ls of Error Control C	odina by M	forgire and	Forral Wiles	India			
		ls of Error Control C	oung by M	iorenta and	ranei, whey	mula			
	Reference Bool	<u> </u>							

Error Correction Coding: Mathematical Methods and Algorithms by Todd.K.
 Moon, Wiley India.

EC 9038: Error Control Coding (Elective) [Mapping between course outcomes (COs) and program outcomes (POs)]

СО	Statement	PO 1	PO 2	PO 3	PSO 1	PSO 2	PSO 3
CO 1	Acquire idea about different types of error control coding techniques.	3	1	1	3	2	1
CO 2	Understand generator matrix, encoding and decoding of different codes.	2	2	2	3	1	2
CO 3	Learn LDPC, BCH, RS and Turbo codes.	2	2	1	3	1	2
CO 4	Analyze and mitigate errors in channels.	3	1	3	3	1	1
CO 5	Differentiate between different coding strategies.	1	1	2	3	2	2
Average		2.2	1.4	1.8	3.0	1.4	1.6